

Author index

Abukawa, I., see Sasaki, M.	82/83 (1994) 387	Chan, SH., S.M. Sze, CY. Chang and	
Akamatsu, M., S. Narahara, T. Kobayashi		WI. Lee, Selective epitaxial growth	
and F. Hasegawa, Optical in-situ		of GaInP by LP-MOCVD using eth-	
analysis of GaAs/AlAs/GaAs and		yldimethylindium, trimethylindium,	
GaAs/(Al)GaAs/GaAs atomic layer		trimethylgallium and triethylgallium	
growth using GaCl ₃ , AlCl ₃ and AsH ₃	82/83 (1994) 228	as group III sources	82/83 (1994) 85
Akazawa, H., Temperature effects on		Chang, CY., see Chan, SH.	82/83 (1994) 85
synchrotron-radiation-excited Si		Choyke, W.J., see Yates, Jr., J.T.	82/83 (1994) 180
atomic layer epitaxy using disilane	82/83 (1994) 394	Chub, A.B., see Khramtsova, E.A.	82/83 (1994) 576
Akinaga, H. and K. Tanaka, Atomic layer		Colter, P.C., see Hayafuji, N.	82/83 (1994) 18
epitaxy of ZnSe using reflectance dif-		Creighton, J.R., Surface stoichiometry	
ference spectroscopy	82/83 (1994) 298	and the role of adsorbates during	
Aleskovski, V.B., see Drozd, V.E.	82/83 (1994) 587	GaAs atomic layer epitaxy	82/83 (1994) 171
Aleskovski, V.B., see Drozd, V.E.	82/83 (1994) 591		,
Aono, M., see Kawai, M.	82/83 (1994) 487	Daté, M., see Taguchi, Y.	82/83 (1994) 434
Aoyagi, Y., see Isshiki, H.	82/83 (1994) 57	DenBaars, S.P., see Keller, B.P.	82/83 (1994) 126
Aoyagi, Y., see Meguro, T.	82/83 (1994) 193	Dillon, A.C., see George, S.M.	82/83 (1994) 460
Aruga, T., see Taguchi, Y.	82/83 (1994) 434	Dip, A., see Hayafuji, N.	82/83 (1994) 18
Asahi, H., see Kim, J.H.	82/83 (1994) 76	Drozd, V.E., A.P. Baraban and I.O. Niki-	02/00 (1771)
Asahi, H., S.G. Kim, M. Seta, K. Asami,	/ (/	forova, Electrical properties of Si-	
H. Watanabe, T. Ogura and S. Gonda,		Al ₂ O ₃ structures grown by ML-ALE	82/83 (1994) 583
Optical properties of atomic layer		Drozd, V.E., A.A. Tulub, V.B. Aleskovski	02/05 (1////500
grown InAs/AlSb quantum well		and D.V. Korol'kov, Synthesis of ox-	
structures by gas source migration en-		ide superalloys by ML-ALE method	82/83 (1994) 587
hanced epitaxy	82/83 (1994) 109	Drozd, V.E. and V.B. Aleskovski, Syn-	02/03 (1774) 301
Asami, K., see Kim, J.H.	82/83 (1994) 76	thesis of conducting oxides by ML-	
Asami, K., see Asahi, H.	82/83 (1994) 109	ALE	82/83 (1994) 591
Asami, S., N.M. Russell, A. Mahajan,	02/03 (1774) 107	ALE	02/03 (1994) 391
P.A. Steiner IV, D.J. Bonser, J.			02 (02 (1004) 250
Fretwell, S. Bannerjee, A. Tasch, J.M.		Ekerdt, J.G., see Asami, S.	82/83 (1994) 359
		El-Masry, N.A., see Bedair, S.M.	82/83 (1994) 7
White and J.G. Ekerdt, Adaptive		El-Masry, N.A., see Hayafuji, N.	82/83 (1994) 18
temperature program ALE of		Eldallal, G.M., see Hayafuji, N.	82/83 (1994) 18
$Si_{1-x}Ge_x/Si$ heterostructures from	92 /92 (1004) 250	Elers, KE., M. Ritala, M. Leskelä and	
Si ₂ H ₆ /Ge ₂ H ₆	82/83 (1994) 359	E. Rauhala, NbCl ₅ as a precursor in	
Asikainen, T., M. Ritala and M. Leskelä,		atomic layer epitaxy	82/83 (1994) 468
Growth of In ₂ S ₃ thin films by atomic	00 (00 (1004) 100	Enta, Y., N. Miyamoto, Y. Takakuwa	
layer epitaxy	82/83 (1994) 122	and H. Kato, Photoelectron intensity	
		oscillation as a probe to monitor Si	
Bannerjee, S., see Asami, S.	82/83 (1994) 359	layer-by-layer growth	82/83 (1994) 327
Baraban, A.P., see Drozd, V.E.	82/83 (1994) 583		
Bedair, S.M. and N.A. El-Masry, Recent		Fahy, M.R., K. Sato and B.A. Joyce, Sili-	
advances in atomic layer epitaxy de-		con doping with modulated beam epi-	
vices	82/83 (1994) 7	taxy in the growth of GaAs(111)A	82/83 (1994) 14
Bedair, S.M., see Hayafuji, N.	82/83 (1994) 18	Fretwell, J., see Asami, S.	82/83 (1994) 359
Bonser, D.J., see Asami, S.	82/83 (1994) 359	Fujita, K., see Hirai, M.	82/83 (1994) 23
,,,	, ,		

Furukawa, H., see Yoshida, I. Furukawa, S., see Hwang, S.M.	82/83 (1994) 501 82/83 (1994) 523	Hongo, S., S. Taniguchi, K. Ojima, T. Urano and T. Kanaji, Adsorption and	
	/ (desorption of H2O on potassium pre-	
Gamo, K., see Meguro, T.	82/83 (1994) 193	covered Si(100)2 × 1 surface	82/83 (1994) 437
Gates, S.M., see Koleske, D.D.	82/83 (1994) 344	Hongo, S., K. Ojima, S. Taniguchi, T.	,
Ge, Q. and P.J. Møller, CO adsorption	/	Urano and T. Kanaji, Observation of	
on clean and atomic-layer-Cu-covered		the interface of Ba/Si(100) by MDS	
ZnO(1010) surfaces	82/83 (1994) 305	and TDS	82/83 (1994) 537
George, S.M., see Okada, L.A.	82/83 (1994) 410	Horikoshi, Y., see Yamaguchi, H.	82/83 (1994) 223
George, S.M., O. Sneh, A.C. Dillon, M.L.	02/03 (1))1/110	Hübner, A., see Yates, Jr., J.T.	82/83 (1994) 180
Wise, A.W. Ott, L.A. Okada and J.D.		Hwang, S.M., A. Izumi, K. Tsutsui and S.	02/ 05 (1774) 100
Way, Atomic layer controlled deposi-		Furukawa, Surface modification of	
tion of SiO ₂ and Al ₂ O ₃ using		CaF ₂ in atomic layer scale by electron	
ABAB binary reaction sequence		beam exposure	82/83 (1994) 523
chemistry	92 /93 (1004) 460	beam exposure	02/03 (1994) 323
	82/83 (1994) 460	Ide, Y. and M. Yamada, Chlorine ad-	
Gonda, S., see Kim, J.H.	82/83 (1994) 76		
Gonda, S., see Asahi, H.	82/83 (1994) 109	sorption on electron beam irradiated	
Goto, H., see Suzuki, T.	82/83 (1994) 103	GaAs photo-oxides: mechanism of in	02 (02 (1004) 210
Goto, K., see Takemi, M.	82/83 (1994) 115	situ EB lithography	82/83 (1994) 310
Goto, S., see Ohno, H.	82/83 (1994) 164	Ikeda, H., Y. Miura, N. Takahashi, A.	
Gotoda, M., H. Sugimoto, S. Maruno, T.		Koukitu and H. Seki, Substitution of	
Isu, W. Susaki and M. Nunoshita,		surface-adsorbed As atoms to P atoms	
Fabrication of smooth facets of InP		in atomic layer epitaxy	82/83 (1994) 257
by selective sidewall epitaxy using		Ikeda, H., see Suda, Y.	82/83 (1994) 332
CBE	82/83 (1994) 80	Imai, S. and M. Matsumura, Hydrogen	
		atom assisted ALE of silicon	82/83 (1994) 322
Hanada, T., see Kawai, M.	82/83 (1994) 487	Imai, S., see Sugahara, S.	82/83 (1994) 380
Hara, K., see Suzuki, T.	82/83 (1994) 103	Inada, T., see Kiyota, Y.	82/83 (1994) 400
Hara, K., see Kano, N.	82/83 (1994) 132	Inoue, N., see Yokoyama, H.	82/83 (1994) 158
Hasegawa, F., see Akamatsu, M.	82/83 (1994) 228	Ishida, M., see Suda, Y.	82/83 (1994) 332
Haukka, S., EL. Lakomaa and T. Sun-		Ishii, M., see Meguro, T.	82/83 (1994) 193
tola, Surface coverage of ALE pre-		Isshiki, H., Y. Aoyagi, T. Sugano, S. Iwai	
cursors on oxides	82/83 (1994) 548	and T. Meguro, Surface processes of	
Hayafuji, N., G.M. Eldallal, A. Dip, P.C.		selective growth by atomic layer epi-	
Colter, N.A. El-Masry and S.M. Be-		taxy	82/83 (1994) 57
dair, Atomic layer epitaxy of device		Isu, T., see Gotoda, M.	82/83 (1994) 80
quality AlGaAs and AlAs	82/83 (1994) 18	Ito, H., see Suzuki, T.	82/83 (1994) 103
Heun, S., M. Sugiyama, S. Maeyama, Y.		Ito, T., K. Shiraishi and T. Ohno, A	,
Watanabe and M. Oshima, Morphol-		Monte Carlo simulation study for	
ogy of epitaxial SrF2 films on atomi-		adatom migration and resultant	
cally modified InP(100)	82/83 (1994) 507	atomic arrangements in Al, Ga1-, As	
Hibino, H. and T. Ogino, Scanning tun-	,,,	on a GaAs(001) surface	82/83 (1994) 208
neling microscopy observations of Ge		Iwai, S., see Isshiki, H.	82/83 (1994) 57
solid-phase epitaxy on Si(111)	82/83 (1994) 374	Iwasa, I., see Otake, S.	82/83 (1994) 263
Himei, H., E. Maruya, M. Kubo, R.	02/00 (2771) 011	Iwata, K., see Kim, J.H.	82/83 (1994) 76
Vetrivel and A. Miyamoto, Theoreti-		Izumi, A., see Hwang, S.M.	82/83 (1994) 523
cal estimation of ordered metal		izum, A., see Hwang, S.M.	02/03 (1994) 323
species in zeolite pores	82/83 (1994) 543	Jimbo, T., see Soga, T.	82/83 (1994) 64
Hirabayashi, I., see Matsubara, M.	82/83 (1994) 494	Joyce, B.A., see Fahy, M.R.	82/83 (1994) 14
Hirai, M., H. Ohnishi, K. Fujita and T.	02/03 (1774) 474	Joyce, B.A., see Pany, W.R.	02/03 (1994) 14
Watanabe, Substrate misorientation		Kanaji, T., see Hongo, S.	82/83 (1994) 437
dependence of thermal stability of Si		Kanaji, T., see Hongo, S.	,
atom in Si atomic layer doped GaAs			82/83 (1994) 537
on GaAs(111)A	82/83 (1994) 23	Kano, N., S. Hirose, K. Hara, J. Yoshino,	
Hirosawa, T., see Yoshida, I.	,	H. Munekata and H. Kukimoto, AlAs	
Hirose, S., see Kano, N.	82/83 (1994) 501	layers with low carbon content grown	
Holmes Jr., A.L., see Keller, B.P.	82/83 (1994) 132 82/83 (1994) 126	by ALE using ethyldimethylamine alane as a new aluminum source	92 (92 (1004) 122
Homma, Y., see Yamaguchi, H.	82/83 (1994) 126		82/83 (1994) 132
riomina, 1., see I aniagueni, fl.	02/03 (1994) 223	Katayama, I., see Ohnishi, H.	82/83 (1994) 444

Katayama, I., see Tanaka, Y.	82/83 (1994) 528	Kujirai, H., see Murakami, E.	82/83 (1994) 338
Katayama, M., see Kawai, M.	82/83 (1994) 487	Kukimoto, H., see Kano, N.	82/83 (1994) 132
Katayama, Y., see Ohno, H.	82/83 (1994) 164	Kumagai, H. and K. Toyoda, In situ ellip-	
Kato, H., see Enta, Y.	82/83 (1994) 327	sometric diagnostics for controlled	
Kawai, M., ZY. Liu, T. Hanada, M.		growth of metal oxides with surface	
Katayama, M. Aono and C.F. Mc-		chemical reactions	82/83 (1994) 481
Conville, Layer controlled growth of		Kurabayashi, T., see Płotka, P.	82/83 (1994) 91
oxide superconductors	82/83 (1994) 487	Kurabayashi, T. and J. Nishizawa, Tem-	
Kawanishi, H., see Takahashi, I.	82/83 (1994) 70	perature synchronized molecular layer	
Kawasaki, M., see Song, Z.	82/83 (1994) 250	epitaxy	82/83 (1994) 97
Keller, B.P., J.C. Yen, A.L. Holmes Jr.,			
S.P. DenBaars and U.K. Mishra, Flow		Lakomaa, EL., see Haukka, S.	82/83 (1994) 548
modulation epitaxy of Ga, In1-, As/		Lazneva, E.F., see Møller, P.J.	82/83 (1994) 569
AlAs heterostructures on InP for res-		Lee, WI., see Chan, SH.	82/83 (1994) 85
onant tunneling diodes	82/83 (1994) 126	Leskelä, M., see Asikainen, T.	82/83 (1994) 122
Khramtsova, E.A., A.V. Zotov, A.A.		Leskelä, M., see Niinistö, L.	82/83 (1994) 454
Saranin, S.V. Ryzhkov, A.B. Chub and		Leskelä, M., see Elers, KE.	82/83 (1994) 468
V.G. Lifshits, Growth of extra-thin		Leskelä, M., see Rautanen, J.	82/83 (1994) 553
ordered aluminum films on Si(111)		Lifshits, V.G., see Khramtsova, E.A.	82/83 (1994) 576
surface	82/83 (1994) 576	Liu, ZY., see Kawai, M.	82/83 (1994) 487
Kim, J.H., H. Asahi, K. Asami, K. Iwata,	,	Lucas, S.R., see Yates, Jr., J.T.	82/83 (1994) 180
S.G. Kim and S. Gonda, Growth tem-		Lujala, V., J. Skarp, M. Tammenmaa and	,
perature dependence of optical prop-		T. Suntola, Atomic layer epitaxy	
erties of gas source MBE grown		growth of doped zinc oxide thin films	
GaP/AIP short period superlattices	82/83 (1994) 76	from organometals	82/83 (1994) 34
Kim, S.G., see Kim, J.H.	82/83 (1994) 76		/ (/
Kim, S.G., see Asahi, H.	82/83 (1994) 109	Maeda, F., see Watanabe, Y.	82/83 (1994) 136
Kimura, S., see Murakami, E.	82/83 (1994) 338	Maeda, F., Y. Watanabe and M. Oshima,	/ (*** **) ***
Kimura, T., see Takemi, M.	82/83 (1994) 115	Surface reactions of Ga and As on	
Kitamura, T., see Sugahara, S.	82/83 (1994) 380	Sb-terminated GaAs(001)	82/83 (1994) 276
Kiyota, Y., T. Nakamura and T. Inada,	02/ 00 (1771) 000	Maeda, H., see Nakayama, H.	82/83 (1994) 214
Boron δ-doping in Si using atmo-		Maeda, Y., see Watamori, M.	82/83 (1994) 417
spheric pressure CVD	82/83 (1994) 400	Maeyama, S., see Heun, S.	82/83 (1994) 507
Kobayashi, M., see Yoshikawa, A.	82/83 (1994) 316	Mahajan, A., see Asami, S.	82/83 (1994) 359
Kobayashi, N. and T. Makimoto, Carbon	/ (/	Makimoto, T., see Kobayashi, N.	82/83 (1994) 284
incorporation mechanism in atomic		Maruno, S., see Gotoda, M.	82/83 (1994) 80
layer epitaxy of GaAs and AlGaAs	82/83 (1994) 284	Maruya, E., see Himei, H.	82/83 (1994) 543
Kobayashi, N., see Uwai, K.	82/83 (1994) 290	Matsubara, M. and I. Hirabayashi,	0=/ 00 (2111) 010
Kobayashi, T., see Akamatsu, M.	82/83 (1994) 228	Preparation of ultra-flat YBCO thin	
Koleske, D.D. and S.M. Gates, Si ALE	02/00 (1)/1/20	films by MOCVD layer-by-layer de-	
using chlorine/hydrogen exchange.		position	82/83 (1994) 494
Fundamentals and films	82/83 (1994) 344	Matsumiya, Y., see Sakuma, Y.	82/83 (1994) 46
Komolov, S.A., see Møller, P.J.	82/83 (1994) 569	Matsumura, M., see Imai, S.	82/83 (1994) 322
Komura, T., see Uesugi, K.	82/83 (1994) 367	Matsumura, M., see Sugahara, S.	82/83 (1994) 380
Kono, S., see Sasaki, M.	82/83 (1994) 387	Matsuura, T., see Suzue, K.	82/83 (1994) 422
Korol'kov, D.V., see Drozd, V.E.	82/83 (1994) 587	McConville, C.F., see Kawai, M.	82/83 (1994) 487
Koukitu, A., see Ikeda, H.	82/83 (1994) 257	Meguro, T., see Isshiki, H.	82/83 (1994) 57
Kubo, M., R. Yamauchi, R. Vetrivel and	02/03 (1774) 237	Meguro, T., M. Ishii, T. Sugano, K. Gamo	02/03 (1774) 31
A. Miyamoto, Formation processes of		and Y. Aoyagi, Control of the etching	
ultrafine metal particles on MgO(100)		reaction of digital etching using tun-	
as investigated by molecular dynamics		able UV laser irradiation	82/83 (1994) 193
and computer graphics	82/83 (1994) 559	Mihashi, Y., see Takemi, M.	82/83 (1994) 115
Kubo, M., see Vetrivel, R.	82/83 (1994) 516	Mishra, U.K., see Keller, B.P.	82/83 (1994) 126
Kubo, M., see Himei, H.	82/83 (1994) 543	Miura, Y., see Ikeda, H.	82/83 (1994) 257
Kubota, H., M. Nagata, R. Miyagawa and	02/03 (1974) 343	Miyagawa, R., see Kubota, H.	82/83 (1994) 565
M.A. Nicolet, Oxidation of TiN thin		Miyamoto, A., see Vetrivel, R.	82/83 (1994) 516
films in an ion-beam-assisted deposi-		Miyamoto, A., see Himei, H.	82/83 (1994) 543
	82/83 (1994) 565	Miyamoto, A., see Kubo, M.	82/83 (1994) 559
tion process	04/03 (1994) 303	whyamoto, A., see Kubo, w.	02/03 (1774) 339

Mochizuki, Y., T. Takada and A. Usui, Theoretical studies on the chloride ALE process Møller, P.J., see Ge, Q. Møller, P.J., see Jed, M. Morishita, M., see Hibino, H. Ogura, T., see Asahi, H. Ohhai, T., see Suzue, K. Ohnishi, H., Y. Yamamoto, I. Katayama, Y. Ohba and K. Oura, Scanning tunneling microscope observations of Si(1113 x-l-Ag and 6 × 1-Ag structures Ohno, H., S. Goto, Y. Nomura, Y. Morishita and Y. Katayama, Kinetics and mechanism of atomic layer epitaxy of GaAs using trimethylgallium Ohno, T., see Ito, T. Ohtau, T., see Vetrivel, R. Ohtau, N., see Sakuma, Y. Nagasawa, H. and Y. Yamaguchi, Mechanisms of SiC growth by alternate supply of SiH ₂ Cl ₂ and C ₂ H ₂ Nagata, M., see Watamori, M. Nakajim, K., see Sakuma, Y. Nakajima, K., see Sakuma, Y. Na	83 (1994) 97 83 (1994) 164 83 (1994) 80 83 (1994) 553
Theoretical studies on the chloride ALE process Møller, P.J., see Ge, Q. Møller, P.J., S.A. Komolov and E.F. Lazneva, Influence of atomic Cu-layer epitaxy on CO ₂ and CO photoin-duced desorption from ZnO(0001) Mori, K., see Takemi, M. Morioka, H., see Watamori, M. Morishita, H., see Tanaka, Y. Morishita, H., see Tanaka, Y. Morishita, H., see Kano, N. Murakami, E., H. Kujirai and S. Kimura, Suppression of HBO ₂ and Sb adsorption on thin-oxide-covered, H-terminated, or Sb-terminated Si(100) surfaces Murota, J., see Sakurab, M. Muto, S., see Sakuma, Y. Muto, S., see Sakuma, Y. Nagasawa, H. and Y. Yamaguchi, Mechanisms of SiC growth by alternate supply of SiH ₂ Cl ₂ and C ₂ H ₂ Nagata, M., see Watamori, M. Nakajim, M., see Sakuma, Y. Nakajima, K., see Sakuma, Y. Nakajima,	83 (1994) 80
ALE process Møller, P.J., see Ge, Q. Møller, P.J., see Ge, Q. Møller, P.J., S.A. Komolov and E.F. Lazneva, Influence of atomic Cu-layer epitaxy on CO ₂ and CO photoin-duced desorption from ZnO(0001) Mori, K., see Takemi, M. Morioka, H., see Watamori, M. Morishita, Y., see Ohno, H. Munekata, H., see Kano, N. Murakami, E., H. Kujirai and S. Kimura, Suppression of HBO ₂ and Sb adsorption on thin-oxide-covered, H-terminated, or Sb-terminated Si(100) surfaces Murota, J., see Sakurab, M. Murota, J., see Sakurab, M. Murota, J., see Sakurab, M. Muto, S., see Sakuma, Y. Muto, S., see Sakuma, Y. Nagasawa, H. and Y. Yamaguchi, Mechanisms of SiC growth by alternate supply of SiH ₂ Cl ₂ and C ₂ H ₂ Nagata, M., see Watamori, M. Nakajima, K., see Sakuma, Y. Nakajima, K.,	
Møller, P.J., see Ge, Q. Møller, P.J., S.A. Komolov and E.F. Lazneva, Influence of atomic Cu-layer epitaxy on CO ₂ and CO photoin-duced desorption from ZnO(0001) Mori, K., see Takemi, M. Morioka, H., see Watamori, M. Morishita, P., see Ohno, H. Mursakami, E., H. Kujirai and S. Kimura, Suppression of HBO ₂ and Sb adsorption on thin-oxide-covered, H-terminated, or Sb-terminated Si(100) surfaces Murota, J., see Sakuraba, M. Murota, J., see Sakuma, Y. Muto, S., see Sakuma, Y. Nagasawa, H. and Y. Yamaguchi, Mechanisms of SiC growth by alternate supply of SiH ₂ Cl ₂ and C ₂ H ₂ Nagata, M., see Watamori, M. Nakajima, K., see Sakuma, Y. Nakajima, K.,	33 (1994) 333
Møller, P.J., S.A. Komolov and E.F. Lazneva, Influence of atomic Cu-layer epitaxy on CO ₂ and CO photoin-duced desorption from ZnO(0001) Mori, K., see Takemi, M. Morioka, H., see Watamori, M. Morishita, H., see Tanaka, Y. Morishita, H., see Kano, N. Murakami, E., H. Kujirai and S. Kimura, Suppression of HBO ₂ and Sb adsorption on thin-oxide-covered, H-terminated, or Sb-terminated Si(100) surfaces Murota, J., see Sakuraba, M. Murota, J., see Suzue, K. 82/83 (1994) 328 Murota, J., see Sakuraba, M. Murota, J., see Sakuma, Y. Muto, S., see Kubota, H. Sa/83 (1994) 405 Nagata, M., see Watamori, M. Nakaji, M., see Watamori, M. Nakajima, K., see Sakuma, Y. Nakajima, K., se	
Lazneva, Influence of atomic Cu-layer epitaxy on CO ₂ and CO photoin-duced desorption from ZnO(0001) Mori, K., see Takemi, M. Morioka, H., see Watamori, M. Morishita, H., see Tanaka, Y. Morishita, H., see Tanaka, Y. Morishita, H., see Tanaka, Y. Morishita, H., see Kohno, H. Munekata, H., see Kohno, H. Murota, J., see Sakuraba, M. Murota, J., see Sakuraba, Y. Muto, S., see Sakuma, Y. Muto, S., see Sakuma, Y. Nagasawa, H. and Y. Yamaguchi, Mechanisms of SiC growth by alternate supply of SiH ₂ Cl ₂ and C ₂ H ₂ Nagata, M., see Watamori, M. Nakajim, M., see Takahashi, I. Nakajima, K., see Sakuma, Y. Nakajima, K., s	
epitaxy on CO ₂ and CO photoin-duced desorption from ZnO(0001) Mori, K., see Takemi, M. Morioka, H., see Watamori, M. Morishita, H., see Watamori, M. Morishita, H., see Tanaka, Y. Morishita, Y., see Ohno, H. Munekata, H., see Kano, N. Murakami, E., H. Kujirai and S. Kimura, Suppression of HBO ₂ and Sb adsorption on thin-oxide-covered, H- terminated, or Sb-terminated Si(100) surfaces Murota, J., see Sakuraba, M. Murota, J., see Sakuraba, M. Muto, S., see Sakuma, Y. Muto, S., see Sakuma, Y. Nagasawa, H. and Y. Yamaguchi, Mechanisms of SiC growth by alternate supply of SiH ₂ Cl ₂ and C ₂ H ₂ Nagata, M., see Kubota, H. Nakajim, M., see Watamori, M. Nakajima, K., see Sakuma, Y. Nakajima, K., see Takah	83 (1994) 374
duced desorption from ZnO(0001) Mori, K., see Takemi, M. Morioka, H., see Watamori, M. Morishita, H., see Tanaka, Y. Morishita, Y., see Ohno, H. Munekata, H., see Kano, N. Murakami, E., H. Kujirai and S. Kimura, Suppression of HBO ₂ and Sb adsorption on thin-oxide-covered, H- terminated, or Sb-terminated Si(100) surfaces Murota, J., see Sakuraba, M. Murota, J., see Sakuraba, M. Murota, J., see Sakuma, Y. Muto, S., see Sakuma, Y. Nagasawa, H. and Y. Yamaguchi, Mechanisms of SiC growth by alternate supply of SiH ₂ Cl ₂ and C ₂ H ₂ Nagata, M., see Kubota, H. Nakajim, M., see Takahashi, I. Nakajima, K., see Sakuma, Y. Nakajima, K., see Sakuma,	83 (1994) 109
Mori, K., see Takemi, M. Morioka, H., see Watamori, M. Morishita, H., see Tanaka, Y. Morishita, Y., see Ohno, H. Murekata, H., see Kano, N. Murakami, E., H. Kujirai and S. Kimura, Suppression of HBO ₂ and Sb adsorption on thin-oxide-covered, H- terminated, or Sb-terminated Si(100) surfaces Murota, J., see Sakuraba, M. Muto, S., see Sakuma, Y. Muto, S., see Sakuma, Y. Muto, S., see Sakuma, Y. Nagasawa, H. and Y. Yamaguchi, Mechanisms of SiC growth by alternate supply of SiH ₂ Cl ₂ and C ₂ H ₂ Nagata, M., see Kubota, H. Nakajim, M., see Sakuma, Y. Nakajima, K., see Sakuma, Y. Nakajima, K.	83 (1994) 444
Morish, K., see Tarkemi, M. Morishita, H., see Watamori, M. Morishita, H., see Tanaka, Y. Morishita, Y., see Ohno, H. Munekata, H., see Kano, N. Murakami, E., H. Kujirai and S. Kimura, Suppression of HBO ₂ and Sb adsorption on thin-oxide-covered, H- terminated, or Sb-terminated Si(100) surfaces Murota, J., see Sakuraba, M. Murota, J., see Sakuraba, M. Murota, J., see Sakuraba, Y. Muto, S., see Sakuma, Y. Muto, S., see Sakuma, Y. Nagasawa, H. and Y. Yamaguchi, Mechanisms of SiC growth by alternate supply of SiH ₂ Cl ₂ and C ₂ H ₂ Nagata, M., see Kubota, H. Nakaji, M., see Takahashi, I. Nakajima, K., see Sakuma, Y.	83 (1994) 422
Morishita, H., see Tanaka, Y. Morishita, H., see Tanaka, Y. Morishita, H., see Ohno, H. Munekata, H., see Kano, N. Murakami, E., H. Kujirai and S. Kimura, Suppression of HBO ₂ and Sb adsorption on thin-oxide-covered, H-terminated, or Sb-terminated Si(100) surfaces Murota, J., see Sakuraba, M. Murota, J., see Sakuraba, M. Muto, S., see Sakuma, Y. Muto, S., see Sakuma, Y. Nagasawa, H. and Y. Yamaguchi, Mechanisms of SiC growth by alternate supply of SiH ₂ Cl ₂ and C ₂ H ₂ Nagata, M., see Kubota, H. Nakaji, M., see Watamori, M. Nakajima, K., see Sakuma, Y.	33 (1994) 23
Morishita, Y., see Ohno, H. Munekata, H., see Kano, N. Murakami, E., H. Kujirai and S. Kimura, Suppression of HBO ₂ and Sb adsorption on thin-oxide-covered, H- terminated, or Sb-terminated Si(100) surfaces Murota, J., see Sakuraba, M. Muto, S., see Sakuma, Y. Muto, S., see Sakuma, Y. Nagasawa, H. and Y. Yamaguchi, Mechanisms of SiC growth by alternate supply of SiH ₂ Cl ₂ and C ₂ H ₂ Nagata, M., see Kubota, H. Nakajim, M., see Takahashi, I. Nakajima, K., see Sakuma, Y.	
Munekata, H., see Kano, N. Murakami, E., H. Kujirai and S. Kimura, Suppression of HBO ₂ and Sb adsorption on thin-oxide-covered, H- terminated, or Sb-terminated Si(100) surfaces Murota, J., see Sakuraba, M. Murota, J., see Sakuraba, M. Muto, S., see Sakuma, Y. Muto, S., see Sakuma, Y. Nagasawa, H. and Y. Yamaguchi, Mechanisms of SiC growth by alternate supply of SiH ₂ Cl ₂ and C ₂ H ₂ Nagata, M., see Kubota, H. Nakajim, M., see Takahashi, I. Nakajima, K., see Sakuma, Y.	
Murakani, E., H. Kujirai and S. Kimura, Suppression of HBO ₂ and Sb adsorption on thin-oxide-covered, H- terminated, or Sb-terminated Si(100) surfaces Murota, J., see Sakuraba, M. Murota, J., see Suzue, K. Muto, S., see Sakuma, Y. Muto, S., see Sakuma, Y. Nagasawa, H. and Y. Yamaguchi, Mechanisms of SiC growth by alternate supply of SiH ₂ Cl ₂ and C ₂ H ₂ Nagata, M., see Kubota, H. Nakajima, K., see Sakuma, Y. Si(111)3 × 1-Ag and 6 × 1-Ag structures Ohno, H., S. Goto, Y. Nomura, Y. Morishita and Y. Katayama, Kinetics and mechanism of atomic layer epitaxy of GaAs using trimethylgallium Ohno, T., see Ito, T. Ohta, T., see Vetrivel, R. Ohtsuka, N., see Sakuma, Y. Ohtsuka, N., see Sakuma, Y. Ojima, K., see Hongo, S. Ojima, K., see Hongo, S. Ojima, K., see Hongo, S. Okada, L.A., M.L. Wise and S.M. George, Isothermal H ₂ desorption kinetics from Si(100)2 × 1: dependence on disilane and atomic hydrogen precursors Raylor of tures 82/8 Ohno, H., S. Goto, Y. Nomura, Y. Morishita and Y. Katayama, Kinetics and mechanism of atomic layer epitaxy of GaAs using trimethylgallium Ohno, T., see Ito, T. Ohta, T., see Vetrivel, R. Ohtsuka, N., see Ozeki, M. Ojima, K., see Hongo, S. Okada, L.A., M.L. Wise and S.M. George, Isothermal H ₂ desorption kinetics from Si(100)2 × 1: dependence on disilane and atomic hydrogen precursors Nagara, M., see Takahashi, I. Nakajima, K., see Sakuma, Y. 82/83 (1994) 405 Nagata, M., see Takahashi, I. 82/83 (1994) 405 Nagata, M., see Takahashi, I. 82/83 (1994) 405 Nagata, M., see George, S.M. Nakajima, K., see Sakuma, Y.	
Suppression of HBO ₂ and Sb adsorption on thin-oxide-covered, H-terminated, or Sb-terminated Si(100) surfaces Murota, J., see Sakuraba, M. Murota, J., see Sakuraba, M. Mutota, J., see Sakuraba, M. Muto, S., see Sakura, Y. Muto, S., see Sakuma, Y. Nagasawa, H. and Y. Yamaguchi, Mechanisms of SiC growth by alternate supply of SiH ₂ Cl ₂ and C ₂ H ₂ Nagata, M., see Kubota, H. Nakaji, M., see Watamori, M. Nakajima, K., see Sakuma, Y. Nakajima,	
tion on thin-oxide-covered, H- terminated, or Sb-terminated Si(100) surfaces Murota, J., see Sakuraba, M. Murota, J., see Suzue, K. Muto, S., see Sakuma, Y. Muto, S., see Sakuma, Y. Nagasawa, H. and Y. Yamaguchi, Mechanisms of SiC growth by alternate supply of SiH ₂ Cl ₂ and C ₂ H ₂ Nagata, M., see Kubota, H. Nakajim, M., see Watamori, M. Nakajima, K., see Sakuma, Y. Nakajima, K., s	83 (1994) 444
terminated, or Sb-terminated Si(100) surfaces Murota, J., see Sakuraba, M. Murota, J., see Suzue, K. Muto, S., see Sakuma, Y. Muto, S., see Sakuma, Y. Nagasawa, H. and Y. Yamaguchi, Mechanisms of SiC growth by alternate supply of SiH ₂ Cl ₂ and C ₂ H ₂ Nagata, M., see Kubota, H. Nakajim, M., see Takahashi, I. Nakajima, K., see Sakuma, Y. Nakajima, K., see Sak	
terminated, or Sb-terminated Si(100) surfaces Murota, J., see Sakuraba, M. Murota, J., see Suzue, K. Muto, S., see Sakuma, Y. Muto, S., see Sakuma, Y. Nagasawa, H. and Y. Yamaguchi, Mechanisms of SiC growth by alternate supply of SiH ₂ Cl ₂ and C ₂ H ₂ Nagata, M., see Kubota, H. Nakaji, M., see Takahashi, I. Nakajima, K., see Sakuma, Y. Nakajima, K., see Sakuma, Y. Nakajima, K., see Sakuma, Y. Salas (1994) 388 Mechanism of atomic layer epitaxy of GaAs using trimethylgallium 82/83 (1994) 422 Ohno, T., see Ito, T. Ohta, T., see Vetrivel, R. Ohtsuka, N., see Sakuma, Y. Ohtsuka, N., see Ozeki, M. Ojima, K., see Hongo, S. Ojima, K., see Hongo, S. Okada, L.A., M.L. Wise and S.M. George, Isothermal H ₂ desorption kinetics from Si(100)2 × 1: dependence on disilane and atomic hydrogen precursors Ondo, S. see Sakuraba, M. Nakajima, K., see Sakuma, Y. Nakajima, K., see Sakuma, Y. Nakajima, K., see Sakuma, Y. Salas (1994) 338 mechanism of atomic layer epitaxy of GaAs using trimethylgallium Ohno, T., see Ito, T. Ohta, T., see Vetrivel, R. Ohtsuka, N., see Ozeki, M. Ojima, K., see Hongo, S. Okada, L.A., M.L. Wise and S.M. George, Isothermal H ₂ desorption kinetics from Si(100)2 × 1: dependence on disilane and atomic hydrogen precursors Okada, L.A., see George, S.M.	
Surfaces Murota, J., see Sakuraba, M. Murota, J., see Suzue, K. Muto, S., see Sakuma, Y. Muto, S., see Sakuma, Y. Muto, S., see Sakuma, Y. Nagasawa, H. and Y. Yamaguchi, Mechanisms of SiC growth by alternate supply of SiH ₂ Cl ₂ and C ₂ H ₂ Nagata, M., see Kubota, H. Nakaji, M., see Watamori, M. Nakajima, K., see Sakuma, Y.	
Murota, J., see Sakuraaa, M. 82/83 (1994) 354 Murota, J., see Suzue, K. 82/83 (1994) 422 Muto, S., see Sakuma, Y. 82/83 (1994) 46 Muto, S., see Sakuma, Y. 82/83 (1994) 239 Nagasawa, H. and Y. Yamaguchi, Mechanisms of SiC growth by alternate supply of SiH ₂ Cl ₂ and C ₂ H ₂ Nagata, M., see Kubota, H. 82/83 (1994) 405 Najata, M., see Watamori, M. 82/83 (1994) 405 Naitoh, M., see Watamori, M. 82/83 (1994) 417 Nakajima, K., see Sakuma, Y. 82/83 (1994) 46 Nakajima, K., see Sakuma, Y. 82/83 (1994) 405 Nakajima, K., see Sakuma, Y.	33 (1994) 164
Muto, S., see Sakuma, Y. Muto, S., see Sakuma, Y. Muto, S., see Sakuma, Y. Nagasawa, H. and Y. Yamaguchi, Mechanisms of SiC growth by alternate supply of SiH ₂ Cl ₂ and C ₂ H ₂ Nagata, M., see Kubota, H. Nakaji, M., see Watamori, M. Nakajima, K., see Sakuma, Y. Nakaj	33 (1994) 208
Muto, S., see Sakuma, Y. Muto, S., see Sakuma, Y. 82/83 (1994) 46 82/83 (1994) 239 Nagasawa, H. and Y. Yamaguchi, Mechanisms of SiC growth by alternate supply of SiH ₂ Cl ₂ and C ₂ H ₂ Nagata, M., see Kubota, H. 82/83 (1994) 405 Naitoh, M., see Watamori, M. Nakaji, M., see Takahashi, I. Nakajima, K., see Sakuma, Y. 82/83 (1994) 46 Nakajima, K., see Sakuma, Y. 82/83 (1994) 470 Nakajima, K., see Sakuma, Y. 82/83 (1994) 46 Nakajima, K., see Sakuma, Y. 82/83 (1994) 470 Nakajima, K., see Sakuma, Y. 82/83 (1994) 46 Nakajima, K., see Sakuma, Y. 82/83 (1994) 470 Nakajima, K., see Sakuma, Y. 82/83 (1994) 46 Nakajima, K., see Sakuma, Y. 82/83 (1994) 405	33 (1994) 516
Nagasawa, H. and Y. Yamaguchi, Mechanisms of SiC growth by alternate supply of SiH ₂ Cl ₂ and C ₂ H ₂ Nagata, M., see Kubota, H. Nakaji, M., see Takahashi, I. Nakajima, K., see Sakuma, Y. Nakajima, K., see Ozeki, M. Ojima, K., see Hongo, S. Okada, L.A., M.L. Wise and S.M. George, Isothermal H ₂ desorption kinetics from Si(100)2 × 1: dependence on disilane and atomic hydrogen precursors	33 (1994) 46
Nagasawa, H. and Y. Yamaguchi, Mechanisms of SiC growth by alternate supply of SiH ₂ Cl ₂ and C ₂ H ₂ Nagata, M., see Kubota, H. Nakaji, M., see Takahashi, I. Nakajima, K., see Sakuma, Y. Nakajima, K., see Hongo, S. Ojima, K., see Hongo, S. Ojima, K., see Hongo, S. Ojima, K., see Hongo, S. Okada, L.A., M.L. Wise and S.M. George, Isothermal H ₂ desorption kinetics from Si(100)2 × 1: dependence on disilane and atomic hydrogen precursors Okada, L.A., see George, S.M. Nakajima, K., see Sakuma, Y. Nakajima, K., see Sakuma, Y. Nakajima, K., see Hongo, S. Ojima, K., see Hongo, S. Okada, L.A., M.L. Wise and S.M. George, Isothermal H ₂ desorption kinetics from Si(100)2 × 1: dependence on disilane and atomic hydrogen precursors Okada, L.A., see George, Isothermal H ₂ desorption kinetics from Si(100)2 × 1: dependence on disilane and atomic hydrogen precursors Okada, L.A., See Hongo, S. Okada, L.A., M.L. Wise and S.M. George, Isothermal H ₂ desorption kinetics from Si(100)2 × 1: dependence on disilane and atomic hydrogen precursors Okada, L.A., See George, Isothermal H ₂ desorption kinetics from Si(100)2 × 1: dependence on disilane and atomic hydrogen precursors Okada, L.A., See Sakuraha M.	33 (1994) 233
Nagasawa, H. and Y. Yamaguchi, Mechanisms of SiC growth by alternate supply of SiH ₂ Cl ₂ and C ₂ H ₂ 82/83 (1994) 405 Nagata, M., see Kubota, H. 82/83 (1994) 565 Naitoh, M., see Watamori, M. 82/83 (1994) 417 Nakaji, M., see Takahashi, I. 82/83 (1994) 70 Nakajima, K., see Sakuma, Y. 82/83 (1994) 46 Nakajima, K., see Sakuma, Y. 82/83 (1994) 239	33 (1994) 437
supply of SiH ₂ Cl ₂ and C ₂ H ₂ Nagata, M., see Kubota, H. Nakaji, M., see Watamori, M. Nakajima, K., see Sakuma, Y.	33 (1994) 537
Supply of SIH ₂ Ct ₂ and C ₂ H ₂ Nagata, M., see Kubota, H. Nakaji, M., see Watamori, M. Nakajima, K., see Sakuma, Y.	
Najata, M., see Kubota, H. 82/83 (1994) 407 Nakaji, M., see Watamori, M. Nakajima, K., see Sakuma, Y. Nakajima, K., see Sakuma, Y. 82/83 (1994) 46 Nakajima, K., see Sakuma, Y. 82/83 (1994) 239 Nakajima, K., see Sakuma, Y. 82/83 (1994) 305 netics from Si(100)2 × 1: dependence on disilane and atomic hydrogen precursors. 82/80 (1994) 46 Nakajima, K., see Sakuma, Y. 82/83 (1994) 239 Nakajima, K., see Sakuma, Y. 82/83 (1994) 239	
Nakaji, M., see Takahashi, I. 82/83 (1994) 70 Nakajima, K., see Sakuma, Y. 82/83 (1994) 46 Nakajima, K., see Sakuma, Y. 82/83 (1994) 239	
Nakajima, K., see Sakuma, Y. Nakajima, K., see Sakuma, Y. Nakajima, K., see Sakuma, Y. 82/83 (1994) 46 Nakajima, K., see Sakuma, Y. 82/83 (1994) 239 Ono. S. see Sakuraha, M. 82/83 (1994) 239	
Nakajima, K., see Sakuma, Y. Nakajima, K., see Sakuma, Y. 82/83 (1994) 239 Okada, L.A., see George, S.M. 82/8 (1994) 239 Ono. S. see Sakuraha, M. 82/8 (1994) 239	3 (1994) 410
(Ino See Sakuraha M X7/)	3 (1994) 460
	3 (1994) 354
Nakamura, 1., see Kiyota, Y. 82/83 (1994) 400 Oshima M. see Watanaha V. 82/83	3 (1994) 136
Nakao, M., see Yoshida, I. 82/83 (1994) 501 Oshima, M., see Watanabe, 1. 0shima, M., see Maeda, F. 82/8	3 (1994) 276
Nakayama, H., M. Tochigi, H. Maeda Oshima, M., see Heun, S. 82/8	3 (1994) 507
and T. Nishino, Configurational Otake, S., A. Sakamoto, M. Yamamoto	
atomic ordering caused by stochastic and I. Iwasa, In-situ observation of	
adsorption processes in MBE-grown Ga adsorption during TMGa expo-	
alloy semiconductors 82/83 (1994) 214 sure on GaAs(001) surfaces with vari-	
Nakazawa, H., see Suemitsu, M. 82/83 (1994) 449 Nakazawa, H., see Suemitsu, M. 82/83 (1994) 449 ous As coverages 82/8	3 (1994) 263
Narahara, S., see Akamatsu, M. 82/83 (1994) 228 Nicolet, M.A., see Kubota, H. 82/83 (1994) 565 Ott, A.W., see George, S.M. 82/8	3 (1994) 460
Niinistö, L. and M. Leskelä, Atomic layer Niinistö, L. and M. Leskelä, Atomic layer	3 (1994) 417
epitaxy in the growth of complex thin	3 (1994) 444
film structures for electroluminescent Oura, K., see Tanaka, Y. 82/8	3 (1994) 528
applications 82/83 (1994) 454 Oyama, Y., P. Plotka and J. Nishizawa,	
Niinistö, L., see Rautanen, J. 82/83 (1994) 553 Selective MLE growth of GaAs and	
Nikiforova, I.O., see Drozd, V.E. 82/83 (1994) 583 surface treatment for ideal static in-	
Nishijima, M., see Taguchi, Y. 82/83 (1994) 434 duction transistor (ISIT) application 82/8	3 (1994) 41
Nishinaga, T. and X.O. Shen, Surface Oyama, Y., see Ptotka, P. 82/8	3 (1994) 91
diffusion and adatom stoichiometry in Ozeki, M., see Sakuma, Y. 82/8	3 (1994) 46
GaAs MBF, studied by microprobe- Ozeki, M. and N. Ohtsuka, Atomic layer	
RHEED/SEM MBE 82/83 (1994) 141 epitaxy of AlAs: growth mechanism 82/8	3 (1994) 233
Nishino, T., see Nakayama, H. 82/83 (1994) 214	
GaAs 82/83 (1994) 1 Plotka, P., T. Kurabayashi, Y. Oyama	3 (1994) 180
Nishizawa, J., see Oyama, Y. 82/83 (1994) 41 and J. Nishizawa, Ideal static induc-	3 (1994) 180

tion transistor implemented with		Shen, X.Q., see Nishinaga, T.	82/83 (1994) 141
molecular layer epitaxy	82/83 (1994) 91	Shigematsu, H., see Sakuma, Y.	82/83 (1994) 46
Plotka, P., see Oyama, Y.	82/83 (1994) 41	Shindo, H., see Seo, A.	82/83 (1994) 475
		Shinohara, M., see Yokoyama, H.	82/83 (1994) 158
Rauhala, E., see Elers, KE.	82/83 (1994) 468	Shiraishi, K., see Ito, T.	82/83 (1994) 208
Rautanen, J., M. Leskelä, L. Niinistö, E.		Shogen, S., see Song, Z.	82/83 (1994) 250
Nykänen, P. Soininen and M. Utri-		Skarp, J., see Lujala, V.	82/83 (1994) 34
ainen, The effect of growth parame-		Sneh, O., see George, S.M.	82/83 (1994) 460
ters on the deposition of CaS thin	/ /	Soga, T., T. Jimbo and M. Umeno, Epi-	
films by atomic layer epitaxy	82/83 (1994) 553	taxial growth of a two-dimensional	
Ritala, M., see Asikainen, T.	82/83 (1994) 122	structure of GaP on a Si substrate by	
Ritala, M., see Elers, KE.	82/83 (1994) 468	metalorganic chemical vapor deposi-	02 (02 (1004) (
Russell, N.M., see Asami, S.	82/83 (1994) 359	tion	82/83 (1994) 64
Ryzhkov, S.V., see Khramtsova, E.A.	82/83 (1994) 576	Soininen, P., see Rautanen, J.	82/83 (1994) 553
0.1	00 (00 (1004) 0(0	Song, Z., S. Shogen, M. Kawasaki and I.	
Sakamoto, A., see Otake, S.	82/83 (1994) 263	Suemune, X-ray photoelectron spec-	
Sakuma, Y., M. Ozeki, N. Ohtsuka, Y.		troscopic and atomic force micro-	
Matsumiya, H. Shigematsu, O. Ueda,		scopic study of GaAs etching with a	02 (02 (1004) 250
S. Muto, K. Nakajima and N.		HCl solution	82/83 (1994) 250
Yokoyama, Pulsed-jet epitaxy: appli-	02 (02 (1004) 46	Steiner IV, P.A., see Asami, S.	82/83 (1994) 359
cation to device processes	82/83 (1994) 46	Suda, Y., M. Ishida, M. Yamashita and	
Sakuma, Y., S. Muto, K. Nakajima and		H. Ikeda, Sub-atomic-layer epitaxy of	02 (02 (1004) 222
N. Yokoyama, A solution to the sur-		Si using Si ₂ H ₆	82/83 (1994) 332
face arsenic stoichiometric problem at		Suemitsu, M., H. Nakazawa and N.	
the GaAs(001) growth surface in	02 (02 (1004) 220	Miyamoto, Temperature-pro-	
atomic layer expitaxy	82/83 (1994) 239	grammed-desorption study of the pro-	
Sakuraba, M., J. Murota, T. Watanabe,		cess of atomic deuterium adsorption	92 /92 (1004) 440
Y. Sawada and S. Ono, Atomic-layer		onto Si(100)2 × 1	82/83 (1994) 449
epitaxy control of Ge and Si in flash-		Suemune, I., Role of a metalorganic As	
heating CVD using GeH ₄ and SiH ₄	92 /92 (1004) 254	source in atomic layer epitaxy of GaAs and AlAs	82/83 (1994) 149
gases	82/83 (1994) 354		82/83 (1994) 250
Saranin, A.A., see Khramtsova, E.A. Sasaki, M., see Yoshida, S.	82/83 (1994) 576 82/83 (1994) 28	Suemune, I., see Song, Z. Sugahara, S., T. Kitamura, S. Imai and	02/03 (1994) 230
Sasaki, M., see Toshida, S. Sasaki, M. and S. Yoshida, Pulsed	02/03 (1994) 20	M. Matsumura, Atomic layer epitaxy	
trimethylgallium scattering from As-		of germanium	82/83 (1994) 380
stabilized and Ga-stabilized surfaces	82/83 (1994) 269	Sugano, T., see Isshiki, H.	82/83 (1994) 57
Sasaki, M., T. Abukawa, H.W. Yeom, M.	02/03 (1774) 207	Sugano, T., see Meguro, T.	82/83 (1994) 193
Yamada, S. Suzuki, S. Sato and S.		Sugimoto, H., see Gotoda, M.	82/83 (1994) 80
Kono, Auger electron diffraction		Sugiyama, M., see Heun, S.	82/83 (1994) 507
study of the initial stage of Ge het-		Suntola, T., see Lujala, V.	82/83 (1994) 34
eroepitaxy on Si(001)	82/83 (1994) 387	Suntola, T., see Haukka, S.	82/83 (1994) 548
Sasaoka, C. and A. Usui, Self-limiting	02/03 (1774) 307	Susaki, W., see Gotoda, M.	82/83 (1994) 80
adsorption of thermally cracked		Suzue, K., T. Matsuura, J. Murota, Y.	02/00 (1771) 00
SiCl ₂ H ₂ on Si surfaces	82/83 (1994) 348	Sawada and T. Ohmi, Substrate ori-	
Sato, K., see Fahy, M.R.	82/83 (1994) 14	entation dependence of self-limited	
Sato, M., Surface structure dependence	02/03 (1771) 11	atomic-layer etching of Si with chlo-	
of O_2 -W adsorption system	82/83 (1994) 532	rine adsorption and low-energy Ar ⁺	
Sato, S., see Sasaki, M.	82/83 (1994) 387	irradiation	82/83 (1994) 422
Sawada, Y., see Sakuraba, M.	82/83 (1994) 354	Suzuki, S., see Sasaki, M.	82/83 (1994) 387
Sawada, Y., see Suzue, K.	82/83 (1994) 422	Suzuki, T., H. Goto, N. Sawaki, H. Ito	02/ 00 (22/ 1/ 00)
Sawaki, N., see Suzuki, T.	82/83 (1994) 103	and K. Hara, Autocompensation in Si	
Schaefer, J., see Yates, Jr., J.T.	82/83 (1994) 180	planar doped GaAs	82/83 (1994) 103
Seki, H., see Ikeda, H.	82/83 (1994) 257	Sze, S.M., see Chan, SH.	82/83 (1994) 85
Seo, A. and H. Shindo, Atomic force		,,	
microscopic study of directional		Taguchi, Y., M. Daté. N. Takagi. T.	
	82/83 (1994) 475	Taguchi, Y., M. Daté, N. Takagi, T. Aruga and M. Nishijima, Chemical	

R30°-B surface: an electron-energy-		Steric and electronic interactions be-	
loss spectroscopy study	82/83 (1994) 434	tween source gas and substrate sur-	
Takada, T., see Mochizuki, Y.	82/83 (1994) 200	face during the Al-CVD/Al selective	
Takagi, N., see Taguchi, Y.	82/83 (1994) 434	epitaxy process as investigated by	
Takahashi, I., M. Nakaji and H. Kawan-		quantum chemical calculations	82/83 (1994) 516
ishi, Migration and related buried		Vetrivel, R., see Himei, H.	82/83 (1994) 543
epitaxy using digital epitaxial growth		Vetrivel, R., see Kubo, M.	82/83 (1994) 559
conditions	82/83 (1994) 70		
Takahashi, N., see Ikeda, H.	82/83 (1994) 257	Watamori, M., M. Naitoh, H. Morioka,	
Takakuwa, Y., see Enta, Y.	82/83 (1994) 327	Y. Maeda and K. Oura, Low temper-	
Takamiya, S., see Takemi, M.	82/83 (1994) 115		
Takemi, M., T. Kimura, K. Mori, K. Goto,		ature adsorption of hydrogen on	
Y. Mihashi and S. Takamiya, Micro-		Si(111) and (100) surfaces studied by elastic recoil detection analysis	92 (92 (1004) 417
scopic analysis of interface structure		•	82/83 (1994) 417
in InGaAs/InP MQW using Pendel-		Watamori, M., see Tanaka, Y.	82/83 (1994) 528
lösung oscillation around a satellite		Watanabe, H., see Asahi, H.	82/83 (1994) 109
peak in high-resolution X-ray diffrac-		Watanabe, T., see Hirai, M.	82/83 (1994) 23
tion	82/83 (1994) 115	Watanabe, T., see Sakuraba, M.	82/83 (1994) 354
Takiguchi, T., K. Uesugi, M. Yoshimura	, , , , , , , , , , , , , , , , , , , ,	Watanabe, Y., F. Maeda and M. Oshima,	
and T. Yao, Atomic-scale modifica-		Comparative study between MEE-	
tion of the AlCl ₃ -adsorbed Si(111)-		and MBE-grown InSb-nanocrystals on	
7×7 surface	82/83 (1994) 428	Se-terminated GaAs(001)	82/83 (1994) 136
Tammenmaa, M., see Lujala, V.	82/83 (1994) 34	Watanabe, Y., see Maeda, F.	82/83 (1994) 276
Tanaka, K., see Akinaga, H.	82/83 (1994) 298	Watanabe, Y., see Heun, S.	82/83 (1994) 507
Tanaka, Y., H. Morishita, M. Watamori,	02/05 (1771) 270	Way, J.D., see George, S.M.	82/83 (1994) 460
K. Oura and I. Katayama, Structural		White, J.M., see Asami, S.	82/83 (1994) 359
study of SrTiO ₃ (100) surfaces by low		Wise, M.L., see Okada, L.A.	82/83 (1994) 410
energy ion scattering	82/83 (1994) 528	Wise, M.L., see George, S.M.	82/83 (1994) 460
Taniguchi, S., see Hongo, S.	82/83 (1994) 437		
Taniguchi, S., see Hongo, S.	82/83 (1994) 537	Yamada, M., see Ide, Y.	82/83 (1994) 310
Tanimoto, M., see Yokoyama, H.	82/83 (1994) 158	Yamada, M., see Sasaki, M.	82/83 (1994) 387
Tasch, A., see Asami, S.	82/83 (1994) 359	Yamaguchi, H., Y. Homma and Y.	02/05 (1774) 507
Tochigi, M., see Nakayama, H.	82/83 (1994) 214	Horikoshi, In-situ monitoring of 1st-	
Tokita, S., see Yoshikawa, A.	82/83 (1994) 316	order phase transition on InAs(001)	
Toyoda, K., see Kumagai, H.	82/83 (1994) 481	surfaces by scanning electron surface	
Tsutsui, K., see Hwang, S.M.	82/83 (1994) 523	microscopy	82/83 (1994) 223
Tulub, A.A., see Drozd, V.E.	82/83 (1994) 587	Yamaguchi, Y., see Nagasawa, H.	82/83 (1994) 405
Tuluo, A.A., see Diozu, V.E.	02/03 (1994) 307	Yamamoto, M., see Otake, S.	82/83 (1994) 263
Ueda, O., see Sakuma, Y.	82/83 (1994) 46	Yamamoto, Y., see Ohnishi, H.	82/83 (1994) 203
Uesugi, K., T. Komura, M. Yoshimura	02/03 (1994) 40	Yamano, H., see Vetrivel, R.	82/83 (1994) 516
and T. Yao, Scanning tunneling mi-		Yamashita, M., see Suda, Y.	,
croscopy study of solid-phase epitaxy		Yamauchi, R., see Vetrivel, R.	82/83 (1994) 332 82/83 (1994) 516
processes of amorphous silicon layers			82/83 (1994) 559
on silicon substrates	92 /92 (1004) 367	Yamauchi, R., see Kubo, M.	,
	82/83 (1994) 367	Yao, T., see Uesugi, K.	82/83 (1994) 367
Uesugi, K., see Takiguchi, T.	82/83 (1994) 428	Yao, T., see Takiguchi, T.	82/83 (1994) 428
Umeno, M., see Soga, T.	82/83 (1994) 64	Yates, Jr., J.T., A. Hübner, S.R. Lucas,	
Urano, T., see Hongo, S.	82/83 (1994) 437	W.D. Partlow, J. Schaefer and W.J.	
Urano, T., see Hongo, S.	82/83 (1994) 537	Choyke, Activation of the Ga-CH ₃	
Usui, A., see Mochizuki, Y.	82/83 (1994) 200	bond using atomic hydrogen – a pos-	
Usui, A., see Sasaoka, C.	82/83 (1994) 348	sible route to III-V semiconductor	()
Utriainen, M., see Rautanen, J.	82/83 (1994) 553	films with low carbon levels	82/83 (1994) 180
Uwai, K. and N. Kobayashi, Real time		Yen, J.C., see Keller, B.P.	82/83 (1994) 126
observation of surface dielectric re-			
0.00 4.700.5		Yeom, H.W., see Sasaki, M.	82/83 (1994) 387
sponses of GaAs(001) using surface		Yokoyama, H., M. Tanimoto, M. Shino-	82/83 (1994) 387
sponses of GaAs(001) using surface photo-absorption	82/83 (1994) 290	Yokoyama, H., M. Tanimoto, M. Shino- hara and N. Inoue, Self-limiting and	82/83 (1994) 387
photo-absorption	82/83 (1994) 290	Yokoyama, H., M. Tanimoto, M. Shino- hara and N. Inoue, Self-limiting and step-propagating nature of GaAs	82/83 (1994) 387
	82/83 (1994) 290	Yokoyama, H., M. Tanimoto, M. Shino- hara and N. Inoue, Self-limiting and	82/83 (1994) 38/ 82/83 (1994) 158

Yokoyama, N., see Sakuma, Y.	82/83 (1994) 46	Yoshida, S., see Sasaki, M.	82/83 (1994) 269
Yokoyama, N., see Sakuma, Y.	82/83 (1994) 239	Yoshikawa, A., M. Kobayashi and S.	
Yoshida, I., H. Furukawa, T. Hirosawa		Tokita, Surface reaction mechanism	
and M. Nakao, Fabrication of CuO2-		in MOMBE-ALE of ZnSe and CdSe	
plane-based high-temperature super-		as determined by a new in-situ optical	
conducting thin films by atomic layer		probing method	82/83 (1994) 316
controlled molecular beam epitaxy	82/83 (1994) 501	Yoshimura, M., see Uesugi, K.	82/83 (1994) 367
Yoshida, S. and M. Sasaki, Investigation		Yoshimura, M., see Takiguchi, T.	82/83 (1994) 428
of a GaN surface structure for the mask of GaAs selective growth using		Yoshino, J., see Kano, N.	82/83 (1994) 132
MOMBE	82/83 (1994) 28	Zotov, A.V., see Khramtsova, E.A.	82/83 (1994) 576

Subject index

Alkali metals		K. Asami, H. Watanabe, T. Ogura	92 /92 /1004) 100
Adsorption and desorption of H ₂ O on potassium precovered Si(100)2 × 1 surface, S. Hongo, S. Taniguchi, K. Ojima, T. Urano and T. Kanaji	82/83 (1994) 437	and S. Gonda Flow modulation epitaxy of Ga _x In _{1-x} As/AlAs heterostructures on InP for resonant tunneling diodes, B.P. Keller, J.C. Yen, A.L. Holmes	82/83 (1994) 109
The effect of growth parameters on the deposition of CaS thin films by atomic layer epitaxy, J. Rautanen, M. Leskelä, L. Niinistö, E. Nykänen, P. Soininen and M. Utriainen		Jr., S.P. DenBaars and U.K. Mishra AlAs layers with low carbon content grown by ALE using ethyldimeth- ylamine alane as a new aluminum source, N. Kano, S. Hirose, K. Hara,	82/83 (1994) 126
	82/83 (1994) 553	J. Yoshino, H. Munekata and H. Kukimoto	82/83 (1994) 132
Alloys		Role of a metalorganic As source in atomic layer epitaxy of GaAs and	
Configurational atomic ordering caused by stochastic adsorption processes in MBE-grown alloy semiconductors, H. Nakayama, M. Tochigi, H. Maeda and		AlAs, I. Suemune A Monte Carlo simulation study for adatom migration and resultant atomic arrangements in Al _x Ga _{1-x} As	82/83 (1994) 149
T. Nishino	82/83 (1994) 214	on a GaAs(001) surface, T. Ito, K.	
Synthesis of oxide superalloys by ML- ALE method, V.E. Drozd, A.A. Tu- lub, V.B. Aleskovski and D.V.	92 (92 (1004) 597	Shiraishi and T. Ohno Optical in-situ analysis of GaAs/AlAs/ GaAs and GaAs/(Al)GaAs/GaAs atomic layer growth using GaCl ₃ ,	82/83 (1994) 208
Korol'kov Aluminium	82/83 (1994) 587	AlCl ₃ and AsH ₃ , M. Akamatsu, S. Narahara, T. Kobayashi and F.	
Aluminum		Hasegawa Atomic layer epitaxy of AlAs: growth	82/83 (1994) 228
Atomic layer epitaxy of device quality AlGaAs and AlAs, N. Hayafuji, G.M.		mechanism, M. Ozeki and N. Oht- suka	82/83 (1994) 233
Eldallal, A. Dip, P.C. Colter, N.A. El-Masry and S.M. Bedair	82/83 (1994) 18	Carbon incorporation mechanism in atomic layer epitaxy of GaAs and Al-	,
Atomic layer epitaxy growth of doped zinc oxide thin films from organomet-		GaAs, N. Kobayashi and T. Maki- moto	82/83 (1994) 284
als, V. Lujala, J. Skarp, M. Tammen- maa and T. Suntola	82/83 (1994) 34	Atomic-scale modification of the AlCl ₃ - adsorbed Si(111)-7 × 7 surface, T.	02/ 03 (1771) 201
Growth temperature dependence of opti- cal properties of gas source MBE	02/03 (1994) 34	Takiguchi, K. Uesugi, M. Yoshimura and T. Yao	82/83 (1994) 428
grown GaP/AlP short period super- lattices, J.H. Kim, H. Asahi, K. Asami,	02 (02 (1004) 76	Steric and electronic interactions be- tween source gas and substrate sur-	
K. Iwata, S.G. Kim and S. Gonda Optical properties of atomic layer grown InAs/AlSb quantum well structures by gas source migration enhanced	82/83 (1994) 76	face during the Al-CVD/Al selective epitaxy process as investigated by quantum chemical calculations, R. Vetrivel, R. Yamauchi, H. Yamano,	
epitaxy, H. Asahi, S.G. Kim, M. Seta,		M. Kubo, A. Miyamoto and T. Ohta	82/83 (1994) 516

Growth of extra-thin ordered aluminum films on Si(111) surface, E.A. Khramtsova, A.V. Zotov, A.A. Saranin, S.V. Ryzhkov, A.B. Chub and		ergy Ar^+ irradiation, K. Suzue, T. Matsuura, J. Murota, Y. Sawada and T. Ohmi	82/83 (1994) 422
V.G. Lifshits	82/83 (1994) 576	Arsenic	
Aluminium oxide		AlAs layers with low carbon content	
Atomic layer controlled deposition of SiO ₂ and Al ₂ O ₃ using ABAB binary reaction sequence chemistry, S.M. George, O. Sneh, A.C. Dillon,		grown by ALE using ethyldimeth- ylamine alane as a new aluminum source, N. Kano, S. Hirose, K. Hara, J. Yoshino, H. Munekata and H. Kukimoto	82/83 (1994) 132
M.L. Wise, A.W. Ott, L.A. Okada and J.D. Way	82/83 (1994) 460	Role of a metalorganic As source in atomic layer epitaxy of GaAs and	02/03 (1774) 132
In situ ellipsometric diagnostics for con- trolled growth of metal oxides with	32, 65 (133.), 166	AlAs, I. Suemune Atomic layer epitaxy of AlAs: growth	82/83 (1994) 149
surface chemical reactions, H. Kuma- gai and K. Toyoda Electrical properties of Si-Al ₂ O ₃ struc-	82/83 (1994) 481	mechanism, M. Ozeki and N. Oht- suka Substitution of surface-adsorbed As	82/83 (1994) 233
tures grown by ML-ALE, V.E. Drozd, A.P. Baraban and I.O. Nikiforova	82/83 (1994) 583	atoms to P atoms in atomic layer epi- taxy, H. Ikeda, Y. Miura, N. Taka- hashi, A. Koukitu and H. Seki	82/83 (1994) 257
Ammonia		Pulsed trimethylgallium scattering from As-stabilized and Ga-stabilized sur-	
Chemical reactivity of the Si(111)- $(\sqrt{3} \times \sqrt{3})$ R30°-B surface: an elec-		faces, M. Sasaki and S. Yoshida Surface reactions of Ga and As on Sb- terminated GaAs(001), F. Maeda, Y.	82/83 (1994) 269
tron-energy-loss spectroscopy study, Y. Taguchi, M. Daté, N. Takagi, T. Aruga and M. Nishijima	82/83 (1994) 434	Watanabe and M. Oshima	82/83 (1994) 276
Aruga and M. Nishijima	82/83 (1994) 434	Atomic force microscopy	
Antimony		Self-limiting and step-propagating nature	
Optical properties of atomic layer grown InAs/AlSb quantum well structures by gas source migration enhanced		of GaAs atomic layer epitaxy revealed by atomic force microscopy, H. Yokoyama, M. Tanimoto, M. Shino-	
epitaxy, H. Asahi, S.G. Kim, M. Seta, K. Asami, H. Watanabe, T. Ogura	92 /92 (1004) 100	hara and N. Inoue X-ray photoelectron spectroscopic and atomic force microscopic study of	82/83 (1994) 158
and S. Gonda Surface reactions of Ga and As on Sb- terminated GaAs(001), F. Maeda, Y.	82/83 (1994) 109	GaAs etching with a HCl solution, Z. Song, S. Shogen, M. Kawasaki and I.	92 (92 (1004) 250
Watanabe and M. Oshima Suppression of HBO ₂ and Sb adsorption on thin-oxide-covered, H-terminated,	82/83 (1994) 276	Suemune Atomic force microscopic study of directional SrSO ₄ (001) surface and its	82/83 (1994) 250
or Sb-terminated Si(100) surfaces, E. Murakami, H. Kujirai and S. Kimura Auger electron diffraction study of the	82/83 (1994) 338	etching property, A. Seo and H. Shindo Preparation of ultra-flat YBCO thin films	82/83 (1994) 475
initial stage of Ge heteroepitaxy on Si(001), M. Sasaki, T. Abukawa, H.W.		by MOCVD layer-by-layer deposition, M. Matsubara and I. Hirabayashi Morphology of epitaxial SrF ₂ films on	82/83 (1994) 494
Yeom, M. Yamada, S. Suzuki, S. Sato and S. Kono	82/83 (1994) 387	atomically modified InP(100), S. Heun, M. Sugiyama, S. Maeyama, Y.	00 (00 (400 () 505
Argon		Watanabe and M. Oshima The effect of growth parameters on the deposition of CaS thin films by atomic	82/83 (1994) 507
Substrate orientation dependence of self-limited atomic-layer etching of Si		layer epitaxy, J. Rautanen, M. Leskelä, L. Niinistö, E. Nykänen, P. Soininen and M. Utriainen	82/83 (1994) 553
with chlorine adsorption and low-en-		Sommen and M. Otriainen	02/03 (1994) 333

Auger electron spectroscopy		Calcium	
Kinetics and mechanism of atomic layer epitaxy of GaAs using trimethylgal- lium, H. Ohno, S. Goto, Y. Nomura, Y. Morishita and Y. Katayama Activation of the Ga-CH ₃ bond using	82/83 (1994) 164	Surface modification of CaF ₂ in atomic layer scale by electron beam exposure, S.M. Hwang, A. Izumi, K. Tsutsui and S. Furukawa	82/83 (1994) 523
atomic hydrogen – a possible route to III-V semiconductor films with low		Carbon	
carbon levels, J.T. Yates, Jr., A. Hübner, S.R. Lucas, W.D. Partlow, J. Schaefer and W.J. Choyke Suppression of HBO ₂ and Sb adsorption on thin-oxide-covered, H-terminated,	82/83 (1994) 180	Carbon incorporation mechanism in atomic layer epitaxy of GaAs and Al- GaAs, N. Kobayashi and T. Maki- moto	82/83 (1994) 284
or Sb-terminated Si(100) surfaces, E. Murakami, H. Kujirai and S. Kimura	82/83 (1994) 338	Carbon dioxide	
Self-limiting adsorption of thermally cracked SiCl ₂ H ₂ on Si surfaces, C.		Influence of atomic Cu-layer epitaxy on CO ₂ and CO photoinduced desorp-	
Sasaoka and A. Usui Adaptive temperature program ALE of Si _{1-r} Ge _r /Si heterostructures from	82/83 (1994) 348	tion from ZnO(0001), P.J. Møller, S.A. Komolov and E.F. Lazneva	82/83 (1994) 569
Si ₂ H ₆ /Ge ₂ H ₆ , S. Asami, N.M. Russell, A. Mahajan, P.A. Steiner IV, D.J.		Carbon monoxide	
Bonser, J. Fretwell, S. Bannerjee, A. Tasch, J.M. White and J.G. Ekerdt Atomic layer epitaxy of germanium, S.	82/83 (1994) 359	CO adsorption on clean and atomic- layer-Cu-covered ZnO(1010) surfaces, Q. Ge and P.J. Møller	82/83 (1994) 305
Sugahara, T. Kitamura, S. Imai and M. Matsumura Auger electron diffraction study of the	82/83 (1994) 380	Influence of atomic Cu-layer epitaxy on CO ₂ and CO photoinduced desorption from ZnO(0001), P.J. Møller,	
initial stage of Ge heteroepitaxy on Si(001), M. Sasaki, T. Abukawa, H.W. Yeom, M. Yamada, S. Suzuki, S. Sato		S.A. Komolov and E.F. Lazneva Chemical vapour deposition	82/83 (1994) 569
and S. Kono Growth of extra-thin ordered aluminum	82/83 (1994) 387		
films on Si(111) surface, E.A. Khramtsova, A.V. Zotov, A.A.		Molecular layer epitaxy of GaAs, J. Nishizawa Recent advances in atomic layer epitaxy	82/83 (1994) 1
Saranin, S.V. Ryzhkov, A.B. Chub and V.G. Lifshits	82/83 (1994) 576	devices, S.M. Bedair and N.A. El- Masry	82/83 (1994) 7
Barium		Surface processes of selective growth by atomic layer epitaxy, H. Isshiki, Y. Aoyagi, T. Sugano, S. Iwai and T.	
Observation of the interface of Ba/ Si(100) by MDS and TDS, S. Hongo, K. Ojima, S. Taniguchi, T. Urano and		Meguro Epitaxial growth of a two-dimensional	82/83 (1994) 57
T. Kanaji	82/83 (1994) 537	structure of GaP on a Si substrate by metalorganic chemical vapor deposi- tion, T. Soga, T. Jimbo and M. Umeno	92 /93 (1004) 64
Boron		Growth temperature dependence of opti-	82/83 (1994) 64
Boron δ-doping in Si using atmospheric pressure CVD, Y. Kiyota, T. Nakamura and T. Inada	82/83 (1994) 400	cal properties of gas source MBE grown Gal'/AlP short period super- lattices, J.H. Kim, H. Asahi, K. Asami,	92 /92 (1004) 74
Cadmium selenide		K. Iwata, S.G. Kim and S. Gonda Fabrication of smooth facets of InP by	82/83 (1994) 76
Surface reaction mechanism in MOMBE-ALE of ZnSe and CdSe as		selective sidewall epitaxy using CBE, M. Gotoda, H. Sugimoto, S. Maruno, T. Isu, W. Susaki and M. Nunoshita	82/83 (1994) 80
determined by a new in-situ optical probing method, A. Yoshikawa, M. Kobayashi and S. Tokita	82/83 (1994) 316	Selective epitaxial growth of GaInP by LP-MOCVD using ethyldimeth- ylindium, trimethylindium, trimethyl-	

gallium and triethylgallium as group III sources, SH. Chan, S.M. Sze,		Otake, A. Sakamoto, M. Yamamoto and I. Iwasa	82/83 (1994) 263
CY. Chang and WI. Lee Temperature synchronized molecular layer epitaxy, T. Kurabayashi and J.	82/83 (1994) 85	Carbon incorporation mechanism in atomic layer epitaxy of GaAs and Al- GaAs, N. Kobayashi and T. Maki-	
Nishizawa Optical properties of atomic layer grown	82/83 (1994) 97	moto Atomic layer epitaxy of ZnSe using re- flectance difference spectroscopy, H.	82/83 (1994) 284
InAs/AISb quantum well structures by gas source migration enhanced epitaxy, H. Asahi, S.G. Kim, M. Seta, K. Asami, H. Watanabe, T. Ogura		Akinaga and K. Tanaka Surface reaction mechanism in MOMBE-ALE of ZnSe and CdSe as	82/83 (1994) 298
and S. Gonda Microscopic analysis of interface struc-	82/83 (1994) 109	determined by a new in-situ optical probing method, A. Yoshikawa, M.	
ture in InGaAs/InP MQW using Pendellösung oscillation around a		Kobayashi and S. Tokita Hydrogen atom assisted ALE of silicon,	82/83 (1994) 316
satellite peak in high-resolution X-ray diffraction, M. Takemi, T. Kimura, K. Mori, K. Goto, Y. Mihashi and S.		S. Imai and M. Matsumura Sub-atomic-layer epitaxy of Si using Si ₂ H ₆ , Y. Suda, M. Ishida, M. Ya-	82/83 (1994) 322
Takamiya Growth of In ₂ S ₃ thin films by atomic	82/83 (1994) 115	mashita and H. Ikeda Si ALE using chlorine/hydrogen ex-	82/83 (1994) 332
layer epitaxy, T. Asikainen, M. Ritala and M. Leskelä Self-limiting and step-propagating nature	82/83 (1994) 122	change. Fundamentals and films, D.D. Koleske and S.M. Gates Self-limiting adsorption of thermally	82/83 (1994) 344
of GaAs atomic layer epitaxy revealed by atomic force microscopy, H.		cracked SiCl ₂ H ₂ on Si surfaces, C. Sasaoka and A. Usui	82/83 (1994) 348
Yokoyama, M. Tanimoto, M. Shino- hara and N. Inoue Kinetics and mechanism of atomic layer	82/83 (1994) 158	Atomic-layer epitaxy control of Ge and Si in flash-heating CVD using GeH ₄ and SiH ₄ gases, M. Sakuraba, J.	
epitaxy of GaAs using trimethylgal- lium, H. Ohno, S. Goto, Y. Nomura,	02 (02 (4004) 464	Murota, T. Watanabe, Y. Sawada and S. Ono	82/83 (1994) 354
Y. Morishita and Y. Katayama Surface stoichiometry and the role of ad- sorbates during GaAs atomic layer	82/83 (1994) 164	Adaptive temperature program ALE of $Si_{1-x}Ge_x/Si$ heterostructures from Si_2H_6/Ge_2H_6 , S. Asami, N.M. Rus-	
epitaxy, J.R. Creighton Theoretical studies on the chloride ALE	82/83 (1994) 171	sell, A. Mahajan, P.A. Steiner IV, D.J. Bonser, J. Fretwell, S. Bannerjee, A.	02 (02 (1004) 250
process, Y. Mochizuki, T. Takada and A. Usui Optical in-situ analysis of GaAs/AlAs/	82/83 (1994) 200	Tasch, J.M. White and J.G. Ekerdt Atomic layer epitaxy of germanium, S. Sugahara, T. Kitamura, S. Imai and	82/83 (1994) 359
GaAs and GaAs/(Al)GaAs/GaAs atomic layer growth using GaCl ₃ , AlCl ₃ and AsH ₃ , M. Akamatsu, S.		M. Matsumura Temperature effects on synchrotron-radi- ation-excited Si atomic layer epitaxy	82/83 (1994) 380
Narahara, T. Kobayashi and F. Hasegawa	82/83 (1994) 228	using disilane, H. Akazawa Boron δ-doping in Si using atmospheric	82/83 (1994) 394
Atomic layer epitaxy of AlAs: growth mechanism, M. Ozeki and N. Oht- suka	82/83 (1994) 233	pressure CVD, Y. Kiyota, T. Naka- mura and T. Inada Mechanisms of SiC growth by alternate	82/83 (1994) 400
A solution to the surface arsenic stoi- chiometric problem at the GaAs(001) growth surface in atomic layer expi-		supply of SiH ₂ Cl ₂ and C ₂ H ₂ , H. Nagasawa and Y. Yamaguchi Isothermal H ₂ desorption kinetics from	82/83 (1994) 405
taxy, Y. Sakuma, S. Muto, K. Naka- jima and N. Yokoyama Substitution of surface-adsorbed As	82/83 (1994) 239	Si(100)2 × 1: dependence on disilane and atomic hydrogen precursors, L.A. Okada, M.L. Wise and S.M. George	82/83 (1994) 410
atoms to P atoms in atomic layer epi- taxy, H. Ikeda, Y. Miura, N. Taka- hashi, A. Koukitu and H. Seki	82/83 (1994) 257	Atomic layer epitaxy in the growth of complex thin film structures for elec- troluminescent applications, L. Niin-	
In-situ observation of Ga adsorption dur- ing TMGa exposure on GaAs(001) surfaces with various As coverages, S.	Su SS (1774) W	istö and M. Leskelä Atomic layer controlled deposition of SiO ₂ and Al ₂ O ₃ using ABAB bi-	82/83 (1994) 454

nary reaction sequence chemistry, S.M. George, O. Sneh, A.C. Dillon, M.L. Wise, A.W. Ott, L.A. Okada and J.D. Way	82/83 (1994) 460	terium adsorption onto $\mathrm{Si}(100)2\times 1,$ M. Suemitsu, H. Nakazawa and N. Miyamoto	82/83 (1994) 449
NbCl ₅ as a precursor in atomic layer epitaxy, KE. Elers, M. Ritala, M. Leskelä and E. Rauhala	82/83 (1994) 468	Doping effects	
Preparation of ultra-flat YBCO thin films by MOCVD layer-by-layer deposition, M. Matsubara and I. Hirabayashi Steric and electronic interactions be- tween source gas and substrate sur- face during the Al-CVD/Al selective	82/83 (1994) 494	Silicon doping with modulated beam epi- taxy in the growth of GaAs(111)A, M.R. Fahy, K. Sato and B.A. Joyce Substrate misorientation dependence of thermal stability of Si atom in Si	82/83 (1994) 14
epitaxy process as investigated by quantum chemical calculations, R. Vetrivel, R. Yamauchi, H. Yamano, M. Kubo, A. Miyamoto and T. Ohta The effect of growth parameters on the	82/83 (1994) 516	atomic layer doped GaAs on GaAs(111)A, M. Hirai, H. Ohnishi, K. Fujita and T. Watanabe Atomic layer epitaxy growth of doped zinc oxide thin films from organomet-	82/83 (1994) 23
deposition of CaS thin films by atomic layer epitaxy, J. Rautanen, M. Leskelä, L. Niinistö, E. Nykänen, P. Soininen and M. Utriainen	82/83 (1994) 553	als, V. Lujala, J. Skarp, M. Tammen- maa and T. Suntola Carbon incorporation mechanism in atomic layer epitaxy of GaAs and Al- GaAs, N. Kobayashi and T. Maki-	82/83 (1994) 34
Clusters		moto Suppression of HBO ₂ and Sb adsorption on thin-oxide-covered, H-terminated,	82/83 (1994) 284
Formation processes of ultrafine metal particles on MgO(100) as investigated by molecular dynamics and computer graphics, M. Kubo, R. Yamauchi, R. Vetrivel and A. Miyamoto	82/83 (1994) 559	or Sb-terminated Si(100) surfaces, E. Murakami, H. Kujirai and S. Kimura Boron δ-doping in Si using atmospheric pressure CVD, Y. Kiyota, T. Nakamura and T. Inada	82/83 (1994) 338 82/83 (1994) 400
Computer simulations		Elastic recoil detection	
Theoretical estimation of ordered metal species in zeolite pores, H. Himei, E. Maruya, M. Kubo, R. Vetrivel and A. Miyamoto	82/83 (1994) 543	Low temperature adsorption of hydrogen on Si(111) and (100) surfaces studied by elastic recoil detection analysis, M. Watamori, M. Naitoh, H. Morioka, Y. Maeda and K. Oura	82/83 (1994) 417
Copper		Electrical properties	
CO adsorption on clean and atomic- layer-Cu-covered ZnO(1010) surfaces,		Ideal static induction transistor imple-	
Q. Ge and P.J. Møller Influence of atomic Cu-layer epitaxy on CO ₂ and CO photoinduced desorp- tion from ZnO(0001), P.J. Møller,	82/83 (1994) 305	mented with molecular layer epitaxy, P. Płotka, T. Kurabayashi, Y. Oyama and J. Nishizawa	82/83 (1994) 91
S.A. Komolov and E.F. Lazneva	82/83 (1994) 569	Flow modulation epitaxy of Ga _x In _{1-x} As/AlAs heterostructures on InP for resonant tunneling diodes,	
Deuterium		B.P. Keller, J.C. Yen, A.L. Holmes Jr., S.P. DenBaars and U.K. Mishra Electrical properties of Si-Al ₂ O ₃ struc-	82/83 (1994) 126
Temperature-programmed-desorption study of the process of atomic deu-		tures grown by ML-ALE, V.E. Drozd, A.P. Baraban and I.O. Nikiforova	82/83 (1994) 583

Electron bombardment

Chlorine adsorption on electron beam irradiated GaAs photo-oxides: mechanism of in situ EB lithography, Y.

Electron energy loss spectroscopy

- Ide and M. Yamada 82/83 (1994) 310
- Chemical reactivity of the Si(111)- $(\sqrt{3} \times \sqrt{3})$ R30°-B surface: an electron-energy-loss spectroscopy study, Y. Taguchi, M. Daté, N. Takagi, T. Aruga and M. Nishijima
- 82/83 (1994) 434

- Electron diffraction
- Silicon doping with modulated beam epitaxy in the growth of GaAs(111)A, M.R. Fahy, K. Sato and B.A. Joyce
- 82/83 (1994) 14
- Influence of atomic Cu-layer epitaxy on CO2 and CO photoinduced desorption from ZnO(0001), P.J. Møller, S.A. Komolov and E.F. Lazneva
 - 82/83 (1994) 569

- Investigation of a GaN surface structure for the mask of GaAs selective growth using MOMBE, S. Yoshida and M. Sasaki
- Comparative study between MEE- and MBE-grown InSb-nanocrystals on Se-terminated GaAs(001), Y. Watanabe, F. Maeda and M. Oshima
- Surface diffusion and adatom stoichiometry in GaAs MBE studied by microprobe-RHEED/SEM MBE, T. Nishinaga and X.Q. Shen
- Surface reactions of Ga and As on Sbterminated GaAs(001), F. Maeda, Y. Watanabe and M. Oshima
- Real time observation of surface dielectric responses of GaAs(001) using surface photo-absorption, K. Uwai and N. Kobayashi
- Atomic layer epitaxy of ZnSe using reflectance difference spectroscopy, H. Akinaga and K. Tanaka
- Sub-atomic-layer epitaxy of Si using SiaHa, Y. Suda, M. Ishida, M. Yamashita and H. Ikeda
- Atomic layer epitaxy of germanium, S. Sugahara, T. Kitamura, S. Imai and M. Matsumura
- Auger electron diffraction study of the initial stage of Ge heteroepitaxy on Si(001), M. Sasaki, T. Abukawa, H.W. Yeom, M. Yamada, S. Suzuki, S. Sato and S. Kono
- Temperature effects on synchrotron-radiation-excited Si atomic layer epitaxy using disilane, H. Akazawa
- Layer controlled growth of oxide superconductors, M. Kawai, Z.-Y. Liu, T. Hanada, M. Katayama, M. Aono and C.F. McConville
- Fabrication of CuO2-plane-based hightemperature superconducting thin films by atomic layer controlled molecular beam epitaxy, I. Yoshida, H. Furukawa, T. Hirosawa and M. Nakao

- 82/83 (1994) 28
- 82/83 (1994) 136
- 82/83 (1994) 141
- 82/83 (1994) 276
- 82/83 (1994) 290
- 82/83 (1994) 298
- 82/83 (1994) 332
- 82/83 (1994) 380
- 82/83 (1994) 387
- 82/83 (1994) 394
- 82/83 (1994) 487
- 82/83 (1994) 501

Epitaxial growth of a two-dimensional structure of GaP on a Si substrate by metalorganic chemical vapor deposi-

Electron microscopy

- tion, T. Soga, T. Jimbo and M. Umeno Migration and related buried epitaxy using digital epitaxial growth conditions. I. Takahashi, M. Nakaji and H. Kawanishi
- Growth of In2S3 thin films by atomic layer epitaxy, T. Asikainen, M. Ritala and M. Leskelä
- Comparative study between MEE- and MBE-grown InSb-nanocrystals on Se-terminated GaAs(001), Y. Watanabe, F. Maeda and M. Oshima
- Surface diffusion and adatom stoichiometry in GaAs MBE studied by microprobe-RHEED/SEM MBE, T. Nishinaga and X.O. Shen
- In-situ monitoring of 1st-order phase transition on InAs(001) surfaces by scanning electron surface microscopy, H. Yamaguchi, Y. Homma and Y. Horikoshi
- Adaptive temperature program ALE of Si_{1-x}Ge_x/Si heterostructures from Si₂H₆/Ge₂H₆, S. Asami, N.M. Russell, A. Mahajan, P.A. Steiner IV, D.J. Bonser, J. Fretwell, S. Bannerjee, A. Tasch, J.M. White and J.G. Ekerdt
- Atomic layer epitaxy of germanium, S. Sugahara, T. Kitamura, S. Imai and M. Matsumura
- Temperature effects on synchrotron-radiation-excited Si atomic layer epitaxy using disilane, H. Akazawa
- NbCl₅ as a precursor in atomic layer epitaxy, K.-E. Elers, M. Ritala, M. Leskelä and E. Rauhala
- Preparation of ultra-flat YBCO thin films by MOCVD layer-by-layer deposition, M. Matsubara and I. Hirabayashi

- 82/83 (1994) 64
- 82/83 (1994) 70
- 82/83 (1994) 122
- 82/83 (1994) 136
- 82/83 (1994) 141
- 82/83 (1994) 223
- 82/83 (1994) 359
- 82/83 (1994) 380
- 82/83 (1994) 394
- 82/83 (1994) 468
- 82/83 (1994) 494

82/83 (1994) 481

82/83 (1994) 587

82/83 (1994) 18

82/83 (1994) 41

82/83 (1994) 46

82/83 (1994) 57

82/83 (1994) 64

82/83 (1994) 70

82/83 (1994) 76

Ellipsometry

In situ ellipsometric diagnostics for controlled growth of metal oxides with surface chemical reactions, H. Kumagai and K. Toyoda

Synthesis of oxide superalloys by ML-ALE method, V.E. Drozd, A.A. Tulub, V.B. Aleskovski and D.V. Korol'kov

Epitaxy

Molecular layer epitaxy of GaAs, J. Nishizawa

Recent advances in atomic layer epitaxy devices, S.M. Bedair and N.A. El-Masry

Silicon doping with modulated beam epitaxy in the growth of GaAs(111)A, M.R. Fahy, K. Sato and B.A. Joyce

Atomic layer epitaxy of device quality AlGaAs and AlAs, N. Hayafuji, G.M. Eldallal, A. Dip, P.C. Colter, N.A. El-Masry and S.M. Bedair

Atomic layer epitaxy growth of doped zinc oxide thin films from organometals, V. Lujala, J. Skarp, M. Tammenmaa and T. Suntola

Selective MLE growth of GaAs and surface treatment for ideal static induction transistor (ISIT) application, Y. Oyama, P. Plotka and J. Nishizawa

Pulsed-jet epitaxy: application to device processes, Y. Sakuma, M. Ozeki, N. Ohtsuka, Y. Matsumiya, H. Shigematsu, O. Ueda, S. Muto, K. Nakajima and N. Yokoyama

Surface processes of selective growth by atomic layer epitaxy, H. Isshiki, Y. Aoyagi, T. Sugano, S. Iwai and T. Meguro

Epitaxial growth of a two-dimensional structure of GaP on a Si substrate by metalorganic chemical vapor deposition, T. Soga, T. Jimbo and M. Umeno

Migration and related buried epitaxy using digital epitaxial growth conditions, I. Takahashi, M. Nakaji and H. Kawanishi

Growth temperature dependence of optical properties of gas source MBE grown GaP/AlP short period superlattices, J.H. Kim, H. Asahi, K. Asami, K. Iwata, S.G. Kim and S. Gonda

Fabrication of smooth facets of InP by selective sidewall epitaxy using CBE, M. Gotoda, H. Sugimoto, S. Maruno, T. Isu, W. Susaki and M. Nunoshita

Selective epitaxial growth of GaInP by LP-MOCVD using ethyldimethylindium, trimethylindium, trimethylgallium and triethylgallium as group III sources, S.-H. Chan, S.M. Sze, C.-Y. Chang and W.-I. Lee

Ideal static induction transistor implemented with molecular layer epitaxy, P. Płotka, T. Kurabayashi, Y. Oyama and J. Nishizawa

Temperature synchronized molecular layer epitaxy, T. Kurabayashi and J. Nishizawa

82/83 (1994) 1 Autocompensation in Si planar doped GaAs, T. Suzuki, H. Goto, N. Sawaki, H. Ito and K. Hara 82/83 (1994) 7 Optical properties of atomic layer grown

InAs/AlSb quantum well structures by gas source migration enhanced epitaxy, H. Asahi, S.G. Kim, M. Seta, K. Asami, H. Watanabe, T. Ogura and S. Gonda

Growth of In₂S₃ thin films by atomic layer epitaxy, T. Asikainen, M. Ritala and M. Leskelä

Flow modulation epitaxy of Ga_xIn_{1-x}As/AlAs heterostructures on InP for resonant tunneling diodes, B.P. Keller, J.C. Yen, A.L. Holmes Jr., S.P. DenBaars and U.K. Mishra

AlAs layers with low carbon content grown by ALE using ethyldimethylamine alane as a new aluminum source, N. Kano, S. Hirose, K. Hara, J. Yoshino, H. Munekata and H.

Comparative study between MEE- and MBE-grown InSb-nanocrystals on Se-terminated GaAs(001), Y. Watanabe, F. Maeda and M. Oshima

Surface diffusion and adatom stoichiometry in GaAs MBE studied by microprobe-RHEED/SEM MBE, T. Nishinaga and X.Q. Shen

Role of a metalorganic As source in atomic layer epitaxy of GaAs and AlAs, I. Suemune

Self-limiting and step-propagating nature of GaAs atomic layer epitaxy revealed by atomic force microscopy, H. Yokoyama, M. Tanimoto, M. Shinohara and N. Inoue

Kinetics and mechanism of atomic layer epitaxy of GaAs using trimethylgallium, H. Ohno, S. Goto, Y. Nomura, Y. Morishita and Y. Katayama 82/83 (1994) 85

82/83 (1994) 80

82/83 (1994) 91

82/83 (1994) 97

82/83 (1994) 103

82/83 (1994) 109

82/83 (1994) 122

82/83 (1994) 126

82/83 (1994) 132

82/83 (1994) 136

82/83 (1994) 141

82/83 (1994) 149

82/83 (1994) 158

82/83 (1994) 164

Surface stoichiometry and the role of ad- sorbates during GaAs atomic layer		substrates, K. Uesugi, T. Komura, M. Yoshimura and T. Yao	82/83 (1994) 367
epitaxy, J.R. Creighton Theoretical studies on the chloride ALE	82/83 (1994) 171	Atomic layer epitaxy of germanium, S. Sugahara, T. Kitamura, S. Imai and	92 (92 (1004) 200
process, Y. Mochizuki, T. Takada and A. Usui Configurational atomic ordering caused by stochastic adsorption processes in	82/83 (1994) 200	M. Matsumura Auger electron diffraction study of the initial stage of Ge heteroepitaxy on Si(001), M. Sasaki, T. Abukawa, H.W.	82/83 (1994) 380
MBE-grown alloy semiconductors, H. Nakayama, M. Tochigi, H. Maeda and T. Nishino	82/83 (1994) 214	Yeom, M. Yamada, S. Suzuki, S. Sato and S. Kono Temperature effects on synchrotron-radi-	82/83 (1994) 387
Optical in-situ analysis of GaAs/AlAs/ GaAs and GaAs/(Al)GaAs/GaAs	02/00 (1771) 211	ation-excited Si atomic layer epitaxy using disilane, H. Akazawa	82/83 (1994) 394
atomic layer growth using GaCl ₃ , AlCl ₃ and AsH ₃ , M. Akamatsu, S.		Mechanisms of SiC growth by alternate supply of SiH ₂ Cl ₂ and C ₂ H ₂ , H. Na-	
Narahara, T. Kobayashi and F. Hasegawa Atomic layer epitaxy of AlAs: growth	82/83 (1994) 228	gasawa and Y. Yamaguchi Atomic layer epitaxy in the growth of complex thin film structures for elec-	82/83 (1994) 405
mechanism, M. Ozeki and N. Oht- suka A solution to the surface arsenic stoi-	82/83 (1994) 233	troluminescent applications, L. Niin- istö and M. Leskelä NbCl ₅ as a precursor in atomic layer	82/83 (1994) 454
chiometric problem at the GaAs(001) growth surface in atomic layer expi-		epitaxy, KE. Elers, M. Ritala, M. Leskelä and E. Rauhala Layer controlled growth of oxide super-	82/83 (1994) 468
taxy, Y. Sakuma, S. Muto, K. Naka- jima and N. Yokoyama Substitution of surface-adsorbed As	82/83 (1994) 239	conductors, M. Kawai, ZY. Liu, T. Hanada, M. Katayama, M. Aono and	
atoms to P atoms in atomic layer epi- taxy, H. Ikeda, Y. Miura, N. Taka- hashi, A. Koukitu and H. Seki	82/83 (1994) 257	C.F. McConville Fabrication of CuO ₂ -plane-based high- temperature superconducting thin	82/83 (1994) 487
Real time observation of surface dielec- tric responses of GaAs(001) using sur- face photo-absorption, K. Uwai and	02,00 (1777) 207	films by atomic layer controlled molecular beam epitaxy, I. Yoshida, H. Furukawa, T. Hirosawa and M.	
N. Kobayashi Atomic layer epitaxy of ZnSe using re-	82/83 (1994) 290	Nakao Morphology of epitaxial SrF ₂ films on	82/83 (1994) 501
flectance difference spectroscopy, H. Akinaga and K. Tanaka Photoelectron intensity oscillation as a	82/83 (1994) 298	atomically modified InP(100), S. Heun, M. Sugiyama, S. Maeyama, Y. Watanabe and M. Oshima	82/83 (1994) 507
probe to monitor Si layer-by-layer growth, Y. Enta, N. Miyamoto, Y. Takakuwa and H. Kato	82/83 (1994) 327	Steric and electronic interactions be- tween source gas and substrate sur- face during the Al-CVD/Al selective	02/ 03 (1774/ 307
Sub-atomic-layer epitaxy of Si using Si ₂ H ₆ , Y. Suda, M. Ishida, M. Ya-		epitaxy process as investigated by quantum chemical calculations, R.	
mashita and H. Ikeda Si ALE using chlorine/hydrogen ex- change. Fundamentals and films, D.D.	82/83 (1994) 332	Vetrivel, R. Yamauchi, H. Yamano, M. Kubo, A. Miyamoto and T. Ohta The effect of growth parameters on the	82/83 (1994) 516
Koleske and S.M. Gates Self-limiting adsorption of thermally cracked SiCl ₂ H ₂ on Si surfaces, C.	82/83 (1994) 344	deposition of CaS thin films by atomic layer epitaxy, J. Rautanen, M. Leskelä, L. Niinistö, E. Nykänen, P.	
Sasaoka and A. Usui Atomic-layer epitaxy control of Ge and Si in flash-heating CVD using GeH ₄ and SiH ₄ gases, M. Sakuraba, J.	82/83 (1994) 348	Soininen and M. Utriainen Influence of atomic Cu-layer epitaxy on CO ₂ and CO photoinduced desorp- tion from ZnO(0001), P.J. Møller,	82/83 (1994) 553
Murota, T. Watanabe, Y. Sawada and S. Ono Scanning tunneling microscopy study of	82/83 (1994) 354	S.A. Komolov and E.F. Lazneva Electrical properties of Si-Al ₂ O ₃ struc- tures grown by ML-ALE, V.E. Drozd,	82/83 (1994) 569
solid-phase epitaxy processes of amorphous silicon layers on silicon		A.P. Baraban and I.O. Nikiforova	82/83 (1994) 583

atomic layer doped GaAs on

GaAs(111)A, M. Hirai, H. Ohnishi,

K. Fujita and T. Watanabe

Etching		Investigation of a GaN surface structure for the mask of GaAs selective growth	
6		using MOMBE, S. Yoshida and M.	
Control of the etching reaction of digital etching using tunable UV laser irradiation, T. Meguro, M. Ishii, T. Sugano,	82/83 (1994) 193	Sasaki Selective MLE growth of GaAs and sur- face treatment for ideal static induc-	82/83 (1994) 28
K. Gamo and Y. Aoyagi X-ray photoelectron spectroscopic and atomic force microscopic study of GaAs etching with a HCl solution, Z.	02/03 (1994) 193	tion transistor (ISIT) application, Y. Oyama, P. Plotka and J. Nishizawa Pulsed-jet epitaxy: application to device	82/83 (1994) 41
Song, S. Shogen, M. Kawasaki and I. Suemune	82/83 (1994) 250	processes, Y. Sakuma, M. Ozeki, N. Ohtsuka, Y. Matsumiya, H. Shigematsu, O. Ueda, S. Muto, K. Naka-	
Substrate orientation dependence of self-limited atomic-layer etching of Si with chlorine adsorption and low-en- ergy Ar ⁺ irradiation, K. Suzue, T.		jima and N. Yokoyama Surface processes of selective growth by atomic layer epitaxy, H. Isshiki, Y. Aoyagi, T. Sugano, S. Iwai and T.	82/83 (1994) 46
Matsuura, J. Murota, Y. Sawada and T. Ohmi	82/83 (1994) 422	Meguro Migration and related buried epitaxy us-	82/83 (1994) 57
Field electron microscopy		ing digital epitaxial growth conditions, I. Takahashi, M. Nakaji and H. Kawanishi	82/83 (1994) 70
Surface structure dependence of ${\rm O_2-W}$ adsorption system, M. Sato	82/83 (1994) 532	Ideal static induction transistor implemented with molecular layer epitaxy, P. Płotka, T. Kurabayashi, Y. Oyama	
Gallium		and J. Nishizawa Temperature synchronized molecular layer epitaxy, T. Kurabayashi and J.	82/83 (1994) 91
Activation of the Ga-CH ₃ bond using atomic hydrogen – a possible route to		Nishizawa Autocompensation in Si planar doped	82/83 (1994) 97
III-V semiconductor films with low carbon levels, J.T. Yates, Jr., A. Hübner, S.R. Lucas, W.D. Partlow, J.		GaAs, T. Suzuki, H. Goto, N. Sawaki, H. Ito and K. Hara Microscopic analysis of interface struc-	82/83 (1994) 103
Schaefer and W.J. Choyke Pulsed trimethylgallium scattering from As-stabilized and Ga-stabilized sur-	82/83 (1994) 180	ture in InGaAs/InP MQW using Pendellösung oscillation around a satellite peak in high-resolution X-ray	
faces, M. Sasaki and S. Yoshida Surface reactions of Ga and As on Sb-	82/83 (1994) 269	diffraction, M. Takemi, T. Kimura, K. Mori, K. Goto, Y. Mihashi and S.	
terminated GaAs(001), F. Maeda, Y. Watanabe and M. Oshima	82/83 (1994) 276	Takamiya Flow modulation epitaxy of Ga _x In _{1-x} As/AlAs heterostructures	82/83 (1994) 115
Gallium arsenide		on InP for resonant tunneling diodes, B.P. Keller, J.C. Yen, A.L. Holmes	92 /92 (1004) 124
Molecular layer epitaxy of GaAs, J. Nishizawa	82/83 (1994) 1	Jr., S.P. DenBaars and U.K. Mishra Comparative study between MEE- and MBE-grown InSb-nanocrystals on	82/83 (1994) 126
Silicon doping with modulated beam epi- taxy in the growth of GaAs(111)A,	92 /92 (1004) 14	Se-terminated GaAs(001), Y. Watan- abe, F. Maeda and M. Oshima	82/83 (1994) 136
M.R. Fahy, K. Sato and B.A. Joyce Atomic layer epitaxy of device quality AlGaAs and AlAs, N. Hayafuji, G.M.	82/83 (1994) 14	Surface diffusion and adatom stoichiom- etry in GaAs MBE studied by micro- probe-RHEED/SEM MBE, T.	
Eldallal, A. Dip, P.C. Colter, N.A. El-Masry and S.M. Bedair Substrate misorientation dependence of	82/83 (1994) 18	Nishinaga and X.Q. Shen Role of a metalorganic As source in atomic layer epitaxy of GaAs and	82/83 (1994) 141
thermal stability of Si atom in Si		AlAs, I. Suemune	82/83 (1994) 149

82/83 (1994) 23

Self-limiting and step-propagating nature

of GaAs atomic layer epitaxy revealed

by atomic force microscopy, H.

Yokoyama, M. Tanimoto, M. Shino- hara and N. Inoue	82/83 (1994) 158	anism of in situ EB lithography, Y. Ide and M. Yamada	82/83 (1994) 310
Kinetics and mechanism of atomic layer epitaxy of GaAs using trimethylgal-	02/03 (1774) 130	Gallium phosphide	02/03 (1774) 310
lium, H. Ohno, S. Goto, Y. Nomura,		Ошит рнозрние	
Y. Morishita and Y. Katayama	82/83 (1994) 164	Epitaxial growth of a two-dimensional	
Surface stoichiometry and the role of ad-		structure of GaP on a Si substrate by	
sorbates during GaAs atomic layer	02 (02 (1004) 171	metalorganic chemical vapor deposi-	
epitaxy, J.R. Creighton Control of the etching reaction of digital	82/83 (1994) 171	tion, T. Soga, T. Jimbo and M. Umeno	82/83 (1994) 64
etching using tunable UV laser irradi-		Growth temperature dependence of opti-	/ (
ation, T. Meguro, M. Ishii, T. Sugano,		cal properties of gas source MBE	
K. Gamo and Y. Aoyagi	82/83 (1994) 193	grown GaP/AlP short period super-	
Theoretical studies on the chloride ALE	,	lattices, J.H. Kim, H. Asahi, K. Asami,	
process, Y. Mochizuki, T. Takada and		K. Iwata, S.G. Kim and S. Gonda	82/83 (1994) 76
A. Usui	82/83 (1994) 200	Selective epitaxial growth of GaInP by	
A Monte Carlo simulation study for		LP-MOCVD using ethyldimeth- ylindium, trimethylindium, trimethyl-	
adatom migration and resultant		gallium and triethylgallium as group	
atomic arrangements in $Al_xGa_{1-x}As$		III sources, SH. Chan, S.M. Sze,	
on a GaAs(001) surface, T. Ito, K. Shiraishi and T. Ohno	82/83 (1994) 208	CY. Chang and WI. Lee	82/83 (1994) 85
Optical in-situ analysis of GaAs/AlAs/	02/03 (1994) 200	-	
GaAs and GaAs/(Al)GaAs/GaAs		Germanium	
atomic layer growth using GaCl ₃ ,			
AlCl ₃ and AsH ₃ , M. Akamatsu, S.		Atomic-layer epitaxy control of Ge and	
Narahara, T. Kobayashi and F.		Si in flash-heating CVD using GeH4	
Hasegawa	82/83 (1994) 228	and SiH ₄ gases, M. Sakuraba, J.	
A solution to the surface arsenic stoi- chiometric problem at the GaAs(001)		Murota, T. Watanabe, Y. Sawada and	
growth surface in atomic layer expi-		S. Ono	82/83 (1994) 354
taxy, Y. Sakuma, S. Muto, K. Naka-		Adaptive temperature program ALE of	
jima and N. Yokoyama	82/83 (1994) 239	$Si_{1-x}Ge_x/Si$ heterostructures from Si_2H_6/Ge_2H_6 , S. Asami, N.M. Rus-	
X-ray photoelectron spectroscopic and		sell, A. Mahajan, P.A. Steiner IV, D.J.	
atomic force microscopic study of		Bonser, J. Fretwell, S. Bannerjee, A.	
GaAs etching with a HCl solution, Z.		Tasch, J.M. White and J.G. Ekerdt	82/83 (1994) 359
Song, S. Shogen, M. Kawasaki and I. Suemune	92 /92 (1004) 250	Scanning tunneling microscopy observa-	
In-situ observation of Ga adsorption dur-	82/83 (1994) 250	tions of Ge solid-phase epitaxy on	
ing TMGa exposure on GaAs(001)		Si(111), H. Hibino and T. Ogino	82/83 (1994) 374
surfaces with various As coverages, S.		Atomic layer epitaxy of germanium, S. Sugahara, T. Kitamura, S. Imai and	
Otake, A. Sakamoto, M. Yamamoto		M. Matsumura	82/83 (1994) 380
and I. Iwasa	82/83 (1994) 263	Auger electron diffraction study of the	02/ 05 (1771) 500
Pulsed trimethylgallium scattering from		initial stage of Ge heteroepitaxy on	
As-stabilized and Ga-stabilized sur-	02 (02 (1004) 2(0	Si(001), M. Sasaki, T. Abukawa, H.W.	
faces, M. Sasaki and S. Yoshida Surface reactions of Ga and As on Sb-	82/83 (1994) 269	Yeom, M. Yamada, S. Suzuki, S. Sato	
terminated GaAs(001), F. Maeda, Y.		and S. Kono	82/83 (1994) 387
Watanabe and M. Oshima	82/83 (1994) 276		
Carbon incorporation mechanism in	/ (//	Halogenides	
atomic layer epitaxy of GaAs and Al-			
GaAs, N. Kobayashi and T. Maki-		Optical in-situ analysis of GaAs/AlAs/	
moto	82/83 (1994) 284	GaAs and GaAs/(Al)GaAs/GaAs	
Real time observation of surface dielec-		atomic layer growth using GaCl ₃ ,	
tric responses of GaAs(001) using sur- face photo-absorption, K. Uwai and		AlCl ₃ and AsH ₃ , M. Akamatsu, S. Narahara, T. Kobayashi and F.	
N. Kobayashi	82/83 (1994) 290	Hasegawa	82/83 (1994) 228
Chlorine adsorption on electron beam	/ 00 (2221) 220	Atomic-scale modification of the AlCl ₃ -	-2/ 00 (2771) 220
irradiated GaAs photo-oxides: mech-		adsorbed Si(111)-7 \times 7 surface, T.	

Takiguchi, K. Uesugi, M. Yoshimura and T. Yao	82/83 (1994) 428	Si ALE using chlorine/hydrogen ex- change. Fundamentals and films, D.D.	
NbCl ₅ as a precursor in atomic layer epitaxy, KE. Elers, M. Ritala, M. Leskelä and E. Rauhala	82/83 (1994) 468	Koleske and S.M. Gates Isothermal H ₂ desorption kinetics from Si(100)2 × 1: dependence on disilane	82/83 (1994) 344
Morphology of epitaxial SrF ₂ films on atomically modified InP(100), S. Heun, M. Sugiyama, S. Maeyama, Y.		and atomic hydrogen precursors, L.A. Okada, M.L. Wise and S.M. George Low temperature adsorption of hydrogen	82/83 (1994) 410
Watanabe and M. Oshima Surface modification of CaF ₂ in atomic layer scale by electron beam expo-	82/83 (1994) 507	on Si(111) and (100) surfaces studied by elastic recoil detection analysis, M. Watamori, M. Naitoh, H. Morioka, Y.	92 (92 (1004) 417
sure, S.M. Hwang, A. Izumi, K. Tsut- sui and S. Furukawa	82/83 (1994) 523	Maeda and K. Oura	82/83 (1994) 417
Halogens		Indium	
Theoretical studies on the chloride ALE process, Y. Mochizuki, T. Takada and A. Usui	82/83 (1994) 200	Selective epitaxial growth of GaInP by LP-MOCVD using ethyldimeth-	
Chlorine adsorption on electron beam irradiated GaAs photo-oxides: mechanism of in situ EB lithography, Y.		ylindium, trimethylindium, trimethyl- gallium and triethylgallium as group III sources, SH. Chan, S.M. Sze, CY. Chang and WI. Lee	82/83 (1994) 85
Ide and M. Yamada Si ALE using chlorine/hydrogen ex-	82/83 (1994) 310	Microscopic analysis of interface struc- ture in InGaAs/InP MQW using	32/ 65 (1771) 65
change. Fundamentals and films, D.D. Koleske and S.M. Gates Substrate orientation dependence of	82/83 (1994) 344	Pendellösung oscillation around a satellite peak in high-resolution X-ray	
self-limited atomic-layer etching of Si with chlorine adsorption and low-en-		diffraction, M. Takemi, T. Kimura, K. Mori, K. Goto, Y. Mihashi and S. Takamiya	82/83 (1994) 115
ergy Ar ⁺ irradiation, K. Suzue, T. Matsuura, J. Murota, Y. Sawada and T. Ohmi	82/83 (1994) 422	Growth of In ₂ S ₃ thin films by atomic layer epitaxy, T. Asikainen, M. Ritala and M. Leskelä	82/83 (1994) 122
Hydrides		Indiana antimonida	
Optical in-situ analysis of GaAs/AlAs/		Indium antimonide	
GaAs and GaAs/(Al)GaAs/GaAs atomic layer growth using GaCl ₃ , AlCl ₃ and AsH ₃ , M. Akamatsu, S.		Comparative study between MEE- and MBE-grown InSb-nanocrystals on Se-terminated GaAs(001), Y. Watan-	
Narahara, T. Kobayashi and F. Hasegawa	82/83 (1994) 228	abe, F. Maeda and M. Oshima	82/83 (1994) 136
Hydrogen		Indium arsenide	
Activation of the Ga-CH ₃ bond using atomic hydrogen – a possible route to III-V semiconductor films with low carbon levels, J.T. Yates, Jr., A. Hübner, S.R. Lucas, W.D. Partlow, J.		Optical properties of atomic layer grown InAs/AlSb quantum well structures by gas source migration enhanced epitaxy, H. Asahi, S.G. Kim, M. Seta,	
Schaefer and W.J. Choyke Hydrogen atom assisted ALE of silicon,	82/83 (1994) 180	K. Asami, H. Watanabe, T. Ogura and S. Gonda	82/83 (1994) 109
S. Imai and M. Matsumura Suppression of HBO ₂ and Sb adsorption on thin-oxide-covered, H-terminated,	82/83 (1994) 322	In-situ monitoring of 1st-order phase transition on InAs(001) surfaces by scanning electron surface microscopy,	
or Sb-terminated Si(100) surfaces, E. Murakami, H. Kujirai and S. Kimura	82/83 (1994) 338	H. Yamaguchi, Y. Homma and Y. Horikoshi	82/83 (1994) 223

Indium phosphide		Adaptive temperature program ALE of Si _{1-x} Ge _x /Si heterostructures from	
Pulsed-jet epitaxy: application to device processes, Y. Sakuma, M. Ozeki, N. Ohtsuka, Y. Matsumiya, H. Shige-		Si ₂ H ₆ /Ge ₂ H ₆ , S. Asami, N.M. Russell, A. Mahajan, P.A. Steiner IV, D.J. Bonser, J. Fretwell, S. Bannerjee, A. Tasch, J.M. White and J.G. Ekerdt	82/83 (1994) 359
matsu, O. Ueda, S. Muto, K. Naka- jima and N. Yokoyama Migration and related buried epitaxy us-	82/83 (1994) 46	Observation of the interface of Ba/Si(100) by MDS and TDS, S. Hongo, K. Ojima, S. Taniguchi, T.	02, 02 (1771, 007
ing digital epitaxial growth conditions, I. Takahashi, M. Nakaji and H. Kawanishi	82/83 (1994) 70	Urano and T. Kanaji	82/83 (1994) 537
Fabrication of smooth facets of InP by selective sidewall epitaxy using CBE,	02/05 (1774)	Ion bombardment	
M. Gotoda, H. Sugimoto, S. Maruno, T. Isu, W. Susaki and M. Nunoshita	82/83 (1994) 80	Substrate orientation dependence of self-limited atomic-layer etching of Si with chlorine adsorption and low-en-	
Microscopic analysis of interface struc- ture in InGaAs/InP MQW using Pendellösung oscillation around a		ergy Ar ⁺ irradiation, K. Suzue, T. Matsuura, J. Murota, Y. Sawada and	
satellite peak in high-resolution X-ray diffraction, M. Takemi, T. Kimura, K.		T. Ohmi Oxidation of TiN thin films in an ion-beam-assisted deposition process, H.	82/83 (1994) 422
Mori, K. Goto, Y. Mihashi and S. Takamiya Flow modulation epitaxy of	82/83 (1994) 115	Kubota, M. Nagata, R. Miyagawa and M.A. Nicolet	82/83 (1994) 565
$Ga_xIn_{1-x}As/AlAs$ heterostructures on InP for resonant tunneling diodes,		Ion scattering	
B.P. Keller, J.C. Yen, A.L. Holmes Jr., S.P. DenBaars and U.K. Mishra Morphology of epitaxial SrF ₂ films on	82/83 (1994) 126	Growth of In ₂ S ₃ thin films by atomic layer epitaxy, T. Asikainen, M. Ritala	
atomically modified InP(100), S. Heun, M. Sugiyama, S. Maeyama, Y. Watanabe and M. Oshima	82/83 (1994) 507	and M. Leskelä NbCl ₅ as a precursor in atomic layer epitaxy, KE. Elers, M. Ritala, M.	82/83 (1994) 122
Infrared spectroscopy	02/03 (1774) 307	Leskelä and E. Rauhala Surface modification of CaF ₂ in atomic layer scale by electron beam expo-	82/83 (1994) 468
Surface stoichiometry and the role of ad-		sure, S.M. Hwang, A. Izumi, K. Tsut- sui and S. Furukawa	82/83 (1994) 523
sorbates during GaAs atomic layer epitaxy, J.R. Creighton	82/83 (1994) 171	Structural study of SrTiO ₃ (100) surfaces by low energy ion scattering, Y. Tanaka, H. Morishita, M. Watamori,	
Atomic layer controlled deposition of SiO ₂ and Al ₂ O ₃ using ABAB binary reaction sequence chemistry,		K. Oura and I. Katayama Surface coverage of ALE precursors on	82/83 (1994) 528
S.M. George, O. Sneh, A.C. Dillon, M.L. Wise, A.W. Ott, L.A. Okada and J.D. Way	82/83 (1994) 460	oxides, S. Haukka, EL. Lakomaa and T. Suntola	82/83 (1994) 548
Surface coverage of ALE precursors on oxides, S. Haukka, EL. Lakomaa and	62/63 (1994) 400	Laser processing	
T. Suntola	82/83 (1994) 548	Control of the etching reaction of digital etching using tunable UV laser irradi- ation, T. Meguro, M. Ishii, T. Sugano,	
Interfaces		K. Gamo and Y. Aoyagi	82/83 (1994) 193
Microscopic analysis of interface struc- ture in InGaAs/InP MQW using Pendellösung oscillation around a		Low energy electron diffraction Low temperature adsorption of hydrogen	
satellite peak in high-resolution X-ray diffraction, M. Takemi, T. Kimura, K.		on Si(111) and (100) surfaces studied by elastic recoil detection analysis, M.	
Mori, K. Goto, Y. Mihashi and S. Takamiya	82/83 (1994) 115	Watamori, M. Naitoh, H. Morioka, Y. Maeda and K. Oura	82/83 (1994) 417

Atomic layer controlled deposition of SiO ₂ and Al ₂ O ₃ using ABAB binary reaction sequence chemistry, S.M. George, O. Sneh, A.C. Dillon, M.L. Wise, A.W. Ott, L.A. Okada and J.D. Way Structural study of SrTiO ₃ (100) surfaces by low energy ion scattering, Y. Tanaka, H. Morishita, M. Watamori,	82/83 (1994) 460	Activation of the Ga-CH ₃ bond using atomic hydrogen – a possible route to III-V semiconductor films with low carbon levels, J.T. Yates, Jr., A. Hübner, S.R. Lucas, W.D. Partlow, J. Schaefer and W.J. Choyke Influence of atomic Cu-layer epitaxy on CO ₂ and CO photoinduced desorption from ZnO(0001), P.J. Møller,	82/83 (1994) 180
K. Oura and I. Katayama Influence of atomic Cu-layer epitaxy on CO ₂ and CO photoinduced desorption from ZnO(0001), P.J. Møller,	82/83 (1994) 528	S.A. Komolov and E.F. Lazneva Metals	82/83 (1994) 569
S.A. Komolov and E.F. Lazneva Growth of extra-thin ordered aluminum films on Si(111) surface, E.A. Khramtsova, A.V. Zotov, A.A. Saranin, S.V. Ryzhkov, A.B. Chub and V.G. Lifshits	82/83 (1994) 569 82/83 (1994) 576	Formation processes of ultrafine metal particles on MgO(100) as investigated by molecular dynamics and computer graphics, M. Kubo, R. Yamauchi, R. Vetrivel and A. Miyamoto	82/83 (1994) 559
Luminescence		Molecular dynamics	
Optical properties of atomic layer grown InAs/AlSb quantum well structures by gas source migration enhanced epitaxy, H. Asahi, S.G. Kim, M. Seta, K. Asami, H. Watanabe, T. Ogura and S. Gonda	82/83 (1994) 109	Theoretical estimation of ordered metal species in zeolite pores, H. Himei, E. Maruya, M. Kubo, R. Vetrivel and A. Miyamoto Formation processes of ultrafine metal particles on MgO(100) as investigated by molecular dynamics and computer	82/83 (1994) 543
Flow modulation epitaxy of $Ga_x In_{1-x}As/AlAs$ heterostructures on InP for resonant tunneling diodes, B.P. Keller, J.C. Yen, A.L. Holmes		graphics, M. Kubo, R. Yamauchi, R. Vetrivel and A. Miyamoto Monte Carlo simulations	82/83 (1994) 559
Jr., S.P. DenBaars and U.K. Mishra Atomic layer epitaxy in the growth of complex thin film structures for elec- troluminescent applications, L. Niin- istö and M. Leskelä Electrical properties of Si-Al ₂ O ₃ struc- tures grown by ML-ALE, V.E. Drozd, A.P. Baraban and I.O. Nikiforova	82/83 (1994) 126 82/83 (1994) 454 82/83 (1994) 583	A Monte Carlo simulation study for adatom migration and resultant atomic arrangements in Al _x Ga _{1-x} As on a GaAs(001) surface, T. Ito, K. Shiraishi and T. Ohno Niobium	82/83 (1994) 208
Magnesium oxide		NbCl ₅ as a precursor in atomic layer	
Formation processes of ultrafine metal particles on MgO(100) as investigated by molecular dynamics and computer graphics, M. Kubo, R. Yamauchi, R. Vetrivel and A. Miyamoto	82/83 (1994) 559	epitaxy, KE. Elers, M. Ritala, M. Leskelä and E. Rauhala Nitrides	82/83 (1994) 468
Mass spectroscopy Molecular layer epitaxy of GaAs, J.		Investigation of a GaN surface structure for the mask of GaAs selective growth using MOMBE, S. Yoshida and M. Sasaki	82/83 (1994) 28
Nishizawa Selective MLE growth of GaAs and sur- face treatment for ideal static induc-	82/83 (1994) 1	Optical properties	
tion transistor (ISIT) application, Y. Oyama, P. Plotka and J. Nishizawa	82/83 (1994) 41	Growth temperature dependence of opti- cal properties of gas source MBE	

grown GaP/AIP short period super-		Role of a metalorganic As source in	
lattices, J.H. Kim, H. Asahi, K. Asami,	92 /92 (1004) 76	atomic layer epitaxy of GaAs and	02 (02 (1004) 140
K. Iwata, S.G. Kim and S. Gonda	82/83 (1994) 76	AlAs, I. Suemune	82/83 (1994) 149
Optical properties of atomic layer grown		Carbon incorporation mechanism in	
InAs/AlSb quantum well structures		atomic layer epitaxy of GaAs and Al-	
by gas source migration enhanced		GaAs, N. Kobayashi and T. Maki-	
epitaxy, H. Asahi, S.G. Kim, M. Seta,		moto	82/83 (1994) 284
K. Asami, H. Watanabe, T. Ogura		Preparation of ultra-flat YBCO thin films	
and S. Gonda	82/83 (1994) 109	by MOCVD layer-by-layer deposition,	
Optical in-situ analysis of GaAs/AlAs/		M. Matsubara and I. Hirabayashi	82/83 (1994) 494
GaAs and GaAs/(Al)GaAs/GaAs		Steric and electronic interactions be-	
atomic layer growth using GaCl ₃ ,		tween source gas and substrate sur-	
AlCl ₃ and AsH ₃ , M. Akamatsu, S.		face during the Al-CVD/Al selective	
Narahara, T. Kobayashi and F.		epitaxy process as investigated by	
	02 (02 (1004) 220		
Hasegawa	82/83 (1994) 228	quantum chemical calculations, R.	
In-situ observation of Ga adsorption dur-		Vetrivel, R. Yamauchi, H. Yamano,	00 100 (100 1) 511
ing TMGa exposure on GaAs(001)		M. Kubo, A. Miyamoto and T. Ohta	82/83 (1994) 516
surfaces with various As coverages, S.		Surface coverage of ALE precursors on	
Otake, A. Sakamoto, M. Yamamoto		oxides, S. Haukka, EL. Lakomaa and	
and I. Iwasa	82/83 (1994) 263	T. Suntola	82/83 (1994) 548
Carbon incorporation mechanism in		Electrical properties of Si-Al ₂ O ₃ struc-	
atomic layer epitaxy of GaAs and Al-		tures grown by ML-ALE, V.E. Drozd,	
GaAs, N. Kobayashi and T. Maki-		A.P. Baraban and I.O. Nikiforova	82/83 (1994) 583
moto	82/83 (1994) 284	Synthesis of oxide superalloys by ML-	02/05 (1771) 505
	02/03 (1994) 204	ALE method, V.E. Drozd, A.A. Tu-	
Atomic layer epitaxy of ZnSe using re-			
flectance difference spectroscopy, H.	00 (00 (4004) 000	lub, V.B. Aleskovski and D.V.	00 (00 (1004) 500
Akinaga and K. Tanaka	82/83 (1994) 298	Korol'kov	82/83 (1994) 587
Surface reaction mechanism in		Synthesis of conducting oxides by ML-	
MOMBE-ALE of ZnSe and CdSe as		ALE, V.E. Drozd and V.B. Aleskovski	82/83 (1994) 591
determined by a new in-situ optical		0.11	
probing method, A. Yoshikawa, M.		Oxides	
Kobayashi and S. Tokita	82/83 (1994) 316		
The effect of growth parameters on the		Chlorine adsorption on electron beam	
deposition of CaS thin films by atomic		irradiated GaAs photo-oxides: mech-	
layer epitaxy, J. Rautanen, M.		anism of in situ EB lithography, Y.	
Leskelä, L. Niinistö, E. Nykänen, P.		Ide and M. Yamada	82/83 (1994) 310
Soininen and M. Utriainen	82/83 (1994) 553	Structural study of SrTiO ₃ (100) surfaces	
Sommen and W. Othanien	02/03 (1774) 333	by low energy ion scattering, Y.	
Organometallia vanour deposition		Tanaka, H. Morishita, M. Watamori,	
Organometallic vapour deposition		K. Oura and I. Katayama	82/83 (1994) 528
		Synthesis of oxide superalloys by ML-	
Atomic layer epitaxy of device quality		ALE method, V.E. Drozd, A.A. Tu-	
AlGaAs and AlAs, N. Hayafuji, G.M.		lub, V.B. Aleskovski and D.V.	
Eldallal, A. Dip, P.C. Colter, N.A.		Korol'kov	82/83 (1994) 587
El-Masry and S.M. Bedair	82/83 (1994) 18		02/03 (1774) 307
Investigation of a GaN surface structure		Synthesis of conducting oxides by ML-	02 (02 (1004) 501
for the mask of GaAs selective growth		ALE, V.E. Drozd and V.B. Aleskovski	82/83 (1994) 591
using MOMBE, S. Yoshida and M.		0	
Sasaki	82/83 (1994) 28	Oxygen	
Atomic layer epitaxy growth of doped	/	Surface atmosture demandance of O. W.	
zinc oxide thin films from organomet-		Surface structure dependence of O ₂ -W	02 (02 (1004) 522
als, V. Lujala, J. Skarp, M. Tammen-		adsorption system, M. Sato	82/83 (1994) 532
maa and T. Suntola	82/83 (1994) 34	DI	
	02/03 (1994) 34	Phase transitions	
AlAs layers with low carbon content		In site, manitoning of 1st andb	
grown by ALE using ethyldimeth-		In-situ monitoring of 1st-order phase	
ylamine alane as a new aluminum		transition on InAs(001) surfaces by	
source, N. Kano, S. Hirose, K. Hara,		scanning electron surface microscopy,	
J. Yoshino, H. Munekata and H.		H. Yamaguchi, Y. Homma and Y.	00 100 1-00 1 0
Kukimoto	82/83 (1994) 132	Horikoshi	82/83 (1994) 223

Atomic layer epitaxy of AlAs: growth mechanism, M. Ozeki and N. Ohtsuka Phosphorus	82/83 (1994) 233	Substrate orientation dependence of self-limited atomic-layer etching of Si with chlorine adsorption and low-en- ergy Ar ⁺ irradiation, K. Suzue, T. Matsuura, J. Murota, Y. Sawada and	
•		T. Ohmi Morphology of epitaxial SrF ₂ films on	82/83 (1994) 422
Substitution of surface-adsorbed As atoms to P atoms in atomic layer epi- taxy, H. Ikeda, Y. Miura, N. Taka-		atomically modified InP(100), S. Heun, M. Sugiyama, S. Maeyama, Y.	
hashi, A. Koukitu and H. Seki	82/83 (1994) 257	Watanabe and M. Oshima Surface modification of CaF ₂ in atomic layer scale by electron beam expo-	82/83 (1994) 507
Photochemistry		sure, S.M. Hwang, A. Izumi, K. Tsut- sui and S. Furukawa	82/83 (1994) 523
Selective MLE growth of GaAs and sur- face treatment for ideal static induc- tion transistor (ISIT) application, Y.		Synthesis of oxide superalloys by ML- ALE method, V.E. Drozd, A.A. Tu- lub, V.B. Aleskovski and D.V.	, , ,
Oyama, P. Plotka and J. Nishizawa Temperature effects on synchrotron-radi- ation-excited Si atomic layer epitaxy	82/83 (1994) 41	Korol'kov	82/83 (1994) 587
using disilane, H. Akazawa	82/83 (1994) 394	Quantum effects	
Photoelectron spectroscopy		Optical properties of atomic layer grown InAs/AISb quantum well structures	
Selective MLE growth of GaAs and sur- face treatment for ideal static induc- tion transistor (ISIT) application, Y.		by gas source migration enhanced epitaxy, H. Asahi, S.G. Kim, M. Seta, K. Asami, H. Watanabe, T. Ogura	
Oyama, P. Plotka and J. Nishizawa Comparative study between MEE- and MBE-grown InSb-nanocrystals on Se-terminated GaAs(001), Y. Watan-	82/83 (1994) 41	and S. Gonda Microscopic analysis of interface struc- ture in InGaAs/InP MQW using Pendellösung oscillation around a	82/83 (1994) 109
abe, F. Maeda and M. Oshima X-ray photoelectron spectroscopic and atomic force microscopic study of GaAs etching with a HCl solution, Z.	82/83 (1994) 136	satellite peak in high-resolution X-ray diffraction, M. Takemi, T. Kimura, K. Mori, K. Goto, Y. Mihashi and S. Takamiya	82/83 (1994) 115
Song, S. Shogen, M. Kawasaki and I. Suemune	82/83 (1994) 250	Radiation damage	
Surface reactions of Ga and As on Sb- terminated GaAs(001), F. Maeda, Y.	92 (92 (1004) 27(Surface modification of CaF ₂ in atomic	
Watanabe and M. Oshima Chlorine adsorption on electron beam irradiated GaAs photo-oxides: mech- anism of in situ EB lithography, Y.	82/83 (1994) 276	layer scale by electron beam expo- sure, S.M. Hwang, A. Izumi, K. Tsut- sui and S. Furukawa	82/83 (1994) 523
Ide and M. Yamada Photoelectron intensity oscillation as a	82/83 (1994) 310	Scanning tunneling microscopy	
probe to monitor Si layer-by-layer growth, Y. Enta, N. Miyamoto, Y.		Scanning tunneling microscopy study of	
Takakuwa and H. Kato Atomic-layer epitaxy control of Ge and Si in flash-heating CVD using GeH ₄	82/83 (1994) 327	solid-phase epitaxy processes of amorphous silicon layers on silicon substrates, K. Uesugi, T. Komura, M.	
and SiH ₄ gases, M. Sakuraba, J. Murota, T. Watanabe, Y. Sawada and S. Ono	82/83 (1994) 354	Yoshimura and T. Yao Scanning tunneling microscopy observa- tions of Ge solid-phase epitaxy on	82/83 (1994) 367
Auger electron diffraction study of the initial stage of Ge heteroepitaxy on Si(001), M. Sasaki, T. Abukawa, H.W. Yeom, M. Yamada, S. Suzuki, S. Sato		Si(111), H. Hibino and T. Ogino Atomic-scale modification of the AlCl ₃ - adsorbed Si(111)-7 × 7 surface, T. Takiguchi, K. Uesugi, M. Yoshimura	82/83 (1994) 374
and S. Kono	82/83 (1994) 387	and T. Yao	82/83 (1994) 428

Scanning tunneling microscope observations of Si(111)3 \times 1-Ag and 6 \times 1-Ag		Temperature effects on synchrotron-radi- ation-excited Si atomic layer epitaxy	
structures, H. Ohnishi, Y. Yamamoto, I. Katayama, Y. Ohba and K. Oura	82/83 (1994) 444	using disilane, H. Akazawa Isothermal H ₂ desorption kinetics from Si(100)2 × 1: dependence on disilane	82/83 (1994) 394
Secondary ion mass spectrometry		and atomic hydrogen precursors, L.A. Okada, M.L. Wise and S.M. George	82/83 (1994) 410
Substrate misorientation dependence of thermal stability of Si atom in Si		Silicon	
atomic layer doped GaAs on GaAs(111)A, M. Hirai, H. Ohnishi,		Silicon doping with modulated beam epi-	
K. Fujita and T. Watanabe	82/83 (1994) 23	taxy in the growth of GaAs(111)A,	02 (02 (1004) 14
Autocompensation in Si planar doped GaAs, T. Suzuki, H. Goto, N. Sawaki,	02/00 (1777) 20	M.R. Fahy, K. Sato and B.A. Joyce Substrate misorientation dependence of thermal stability of Si atom in Si	82/83 (1994) 14
H. Ito and K. Hara Boron δ-doping in Si using atmospheric	82/83 (1994) 103	atomic layer doped GaAs on GaAs(111)A, M. Hirai, H. Ohnishi,	
pressure CVD, Y. Kiyota, T. Naka- mura and T. Inada	82/83 (1994) 400	K. Fujita and T. Watanabe Epitaxial growth of a two-dimensional	82/83 (1994) 23
Selenium		structure of GaP on a Si substrate by metalorganic chemical vapor deposi- tion, T. Soga, T. Jimbo and M. Umeno	82/83 (1994) 64
Comparative study between MEE- and		Autocompensation in Si planar doped	
MBE-grown InSb-nanocrystals on Se-terminated GaAs(001), Y. Watan-		GaAs, T. Suzuki, H. Goto, N. Sawaki, H. Ito and K. Hara	82/83 (1994) 103
abe, F. Maeda and M. Oshima	82/83 (1994) 136	Hydrogen atom assisted ALE of silicon, S. Imai and M. Matsumura	82/83 (1994) 322
Atomic layer epitaxy of ZnSe using re- flectance difference spectroscopy, H.	92 /92 (1004) 209	Photoelectron intensity oscillation as a probe to monitor Si layer-by-layer	02/00 (1771) 022
Akinaga and K. Tanaka Surface reaction mechanism in	82/83 (1994) 298	growth, Y. Enta, N. Miyamoto, Y.	02 (02 (1004) 227
MOMBE-ALE of ZnSe and CdSe as determined by a new in-situ optical		Takakuwa and H. Kato Sub-atomic-layer epitaxy of Si using	82/83 (1994) 327
probing method, A. Yoshikawa, M.		Si ₂ H ₆ , Y. Suda, M. Ishida, M. Ya- mashita and H. Ikeda	82/83 (1994) 332
Kobayashi and S. Tokita	82/83 (1994) 316	Suppression of HBO ₂ and Sb adsorption on thin-oxide-covered, H-terminated,	02/00 (1771/002
Semiconductors		or Sb-terminated Si(100) surfaces, E. Murakami, H. Kujirai and S. Kimura	82/83 (1994) 338
Activation of the Ga-CH3 bond using		Si ALE using chlorine/hydrogen ex-	
atomic hydrogen – a possible route to III-V semiconductor films with low		change. Fundamentals and films, D.D. Koleske and S.M. Gates	82/83 (1994) 344
carbon levels, J.T. Yates, Jr., A.		Self-limiting adsorption of thermally	,
Hübner, S.R. Lucas, W.D. Partlow, J.		cracked SiCl ₂ H ₂ on Si surfaces, C.	02 (02 (1004) 240
Schaefer and W.J. Choyke	82/83 (1994) 180	Sasaoka and A. Usui Atomic-layer epitaxy control of Ge and	82/83 (1994) 348
Configurational atomic ordering caused by stochastic adsorption processes in		Si in flash-heating CVD using GeH ₄	
MBE-grown alloy semiconductors, H.		and SiH ₄ gases, M. Sakuraba, J.	
Nakayama, M. Tochigi, H. Maeda and		Murota, T. Watanabe, Y. Sawada and	22 (22 (4224) 254
T. Nishino	82/83 (1994) 214	S. Ono Adaptive temperature program ALE of	82/83 (1994) 354
		Si _{1-x} Ge _x /Si heterostructures from	
Silane		Si ₂ H ₆ /Ge ₂ H ₆ , S. Asami, N.M. Rus-	
		sell, A. Mahajan, P.A. Steiner IV, D.J.	
Atomic-layer epitaxy control of Ge and Si in flash-heating CVD using GeH ₄		Bonser, J. Fretwell, S. Bannerjee, A. Tasch, J.M. White and J.G. Ekerdt	82/83 (1994) 359
and SiH_4 gases, M. Sakuraba, J.		Scanning tunneling microscopy study of	02/03 (1774) 337
Murota, T. Watanabe, Y. Sawada and		solid-phase epitaxy processes of	
S. Ono	82/83 (1994) 354	amorphous silicon layers on silicon	

substrates, K. Uesugi, T. Komura, M. Yoshimura and T. Yao Scanning tunneling microscopy observa-	82/83 (1994) 367	Electrical properties of Si-Al ₂ O ₃ structures grown by ML-ALE, V.E. Drozd, A.P. Baraban and I.O. Nikiforova	82/83 (1994) 583
tions of Ge solid-phase epitaxy on			
Si(111), H. Hibino and T. Ogino Temperature effects on synchrotron-radi-	82/83 (1994) 374	Silicon carbide	
ation-excited Si atomic layer epitaxy		14 1 1 4 6 6 6 6 1 1 1 1 1 1 1 1 1 1 1 1	
using disilane, H. Akazawa Boron δ-doping in Si using atmospheric pressure CVD, Y. Kiyota, T. Naka-	82/83 (1994) 394	Mechanisms of SiC growth by alternate supply of SiH ₂ Cl ₂ and C ₂ H ₂ , H. Na- gasawa and Y. Yamaguchi	82/83 (1994) 405
mura and T. Inada	82/83 (1994) 400		
Isothermal H_2 desorption kinetics from $Si(100)2 \times 1$: dependence on disilane	/ (//	Silicon oxide	
and atomic hydrogen precursors, L.A.	92 /92 (1004) 410	Atomic layer controlled deposition of	
Okada, M.L. Wise and S.M. George Low temperature adsorption of hydrogen on Si(111) and (100) surfaces studied	82/83 (1994) 410	SiO ₂ and Al ₂ O ₃ using ABAB binary reaction sequence chemistry, S.M. George, O. Sneh, A.C. Dillon,	
by elastic recoil detection analysis, M.		M.L. Wise, A.W. Ott, L.A. Okada	
Watamori, M. Naitoh, H. Morioka, Y. Maeda and K. Oura	82/83 (1994) 417	and J.D. Way	82/83 (1994) 460
Substrate orientation dependence of	02/03 (1994) 417		
self-limited atomic-layer etching of Si		Silver	
with chlorine adsorption and low-en-			
ergy Ar ⁺ irradiation, K. Suzue, T. Matsuura, J. Murota, Y. Sawada and		Scanning tunneling microscope observa- tions of Si(111)3 \times 1-Ag and 6 \times 1-Ag	
T. Ohmi	82/83 (1994) 422	structures, H. Ohnishi, Y. Yamamoto,	
Atomic-scale modification of the AlCl ₃ - adsorbed Si(111)-7 × 7 surface, T.	02/03 (1774) 422	I. Katayama, Y. Ohba and K. Oura	82/83 (1994) 444
Takiguchi, K. Uesugi, M. Yoshimura and T. Yao	82/83 (1994) 428	Sputter deposition	
Chemical reactivity of the Si(111)-	02/00 (1771) 120		
$(\sqrt{3} \times \sqrt{3})$ R30°-B surface: an elec-		Oxidation of TiN thin films in an ion-	
tron-energy-loss spectroscopy study,		beam-assisted deposition process, H. Kubota, M. Nagata, R. Miyagawa and	
Y. Taguchi, M. Daté, N. Takagi, T.	00 (00 (4004) 404	M.A. Nicolet	82/83 (1994) 565
Aruga and M. Nishijima	82/83 (1994) 434	171.7 1. 17100101	02/05 (1774) 505
Adsorption and desorption of H_2O on potassium precovered $Si(100)2 \times 1$		Strontium	
surface, S. Hongo, S. Taniguchi, K.		Stromum	
Ojima, T. Urano and T. Kanaji	82/83 (1994) 437	Atomic force microscopic study of direc-	
Scanning tunneling microscope observa-		tional SrSO ₄ (001) surface and its	
tions of Si(111)3 \times 1-Ag and 6 \times 1-Ag		etching property, A. Seo and H.	
structures, H. Ohnishi, Y. Yamamoto,	02 (02 (1004) 111	Shindo	82/83 (1994) 475
I. Katayama, Y. Ohba and K. Oura Temperature-programmed-desorption	82/83 (1994) 444	Morphology of epitaxial SrF ₂ films on	
study of the process of atomic deu-		atomically modified InP(100), S.	
terium adsorption onto $Si(100)2 \times 1$,		Heun, M. Sugiyama, S. Maeyama, Y.	92 /92 (1004) 507
M. Suemitsu, H. Nakazawa and N.		Watanabe and M. Oshima Structural study of SrTiO ₃ (100) surfaces	82/83 (1994) 507
Miyamoto	82/83 (1994) 449	by low energy ion scattering, Y.	
Observation of the interface of		Tanaka, H. Morishita, M. Watamori,	
Ba/Si(100) by MDS and TDS, S.		K. Oura and I. Katayama	82/83 (1994) 528
Hongo, K. Ojima, S. Taniguchi, T. Urano and T. Kanaji	92 /92 (1004) 527		
Growth of extra-thin ordered aluminum	82/83 (1994) 537	Sulphides	
films on Si(111) surface, E.A.			
Khramtsova, A.V. Zotov, A.A.		Growth of In2S3 thin films by atomic	
Saranin, S.V. Ryzhkov, A.B. Chub and		layer epitaxy, T. Asikainen, M. Ritala	
V.G. Lifshits	82/83 (1994) 576	and M. Leskelä	82/83 (1994) 122

The effect of growth parameters on the deposition of CaS thin films by atomic		Surface diffusion	
layer epitaxy, J. Rautanen, M. Leskelä, L. Niinistö, E. Nykänen, P. Soininen and M. Utriainen	82/83 (1994) 553	Surface diffusion and adatom stoichiom- etry in GaAs MBE studied by micro- probe-RHEED/SEM MBE, T. Nishinaga and X.Q. Shen	82/83 (1994) 141
Sulphur		Thermal desorption	
Atomic force microscopic study of directional SrSO ₄ (001) surface and its etching property, A. Seo and H. Shindo	82/83 (1994) 475	Role of a metalorganic As source in atomic layer epitaxy of GaAs and AlAs, I. Suemune Activation of the Ga-CH ₃ bond using atomic hydrogen – a possible route to	82/83 (1994) 149
Superconductivity Layer controlled growth of oxide super-		III-V semiconductor films with low carbon levels, J.T. Yates, Jr., A. Hübner, S.R. Lucas, W.D. Partlow, J. Schoofer, and W.L. Cheville.	92 /92 (1004) 190
conductors, M. Kawai, ZY. Liu, T. Hanada, M. Katayama, M. Aono and		Schaefer and W.J. Choyke CO adsorption on clean and atomic- layer-Cu-covered ZnO(1010) surfaces,	82/83 (1994) 180
 C.F. McConville Preparation of ultra-flat YBCO thin films by MOCVD layer-by-layer deposition, 	82/83 (1994) 487	Q. Ge and P.J. Møller Self-limiting adsorption of thermally cracked SiCl ₂ H ₂ on Si surfaces, C.	82/83 (1994) 305
M. Matsubara and I. Hirabayashi Fabrication of CuO ₂ -plane-based high- temperature superconducting thin films by atomic layer controlled molecular beam epitaxy, I. Yoshida,	82/83 (1994) 494	Sasaoka and A. Usui Adaptive temperature program ALE of Si _{1-x} Ge _x /Si heterostructures from Si ₂ H ₆ /Ge ₂ H ₆ , S. Asami, N.M. Russell, A. Mahajan, P.A. Steiner IV, D.J.	82/83 (1994) 348
H. Furukawa, T. Hirosawa and M. Nakao	82/83 (1994) 501	Bonser, J. Fretwell, S. Bannerjee, A. Tasch, J.M. White and J.G. Ekerdt Isothermal H ₂ desorption kinetics from	82/83 (1994) 359
Superlattices		Si(100)2 × 1: dependence on disilane and atomic hydrogen precursors, L.A. Okada, M.L. Wise and S.M. George Adsorption and desorption of H ₂ O on	82/83 (1994) 410
Pulsed-jet epitaxy: application to device processes, Y. Sakuma, M. Ozeki, N. Ohtsuka, Y. Matsumiya, H. Shige- matsu, O. Ueda, S. Muto, K. Naka-		potassium precovered Si(100)2 × 1 surface, S. Hongo, S. Taniguchi, K. Ojima, T. Urano and T. Kanaji	82/83 (1994) 437
jima and N. Yokoyama Growth temperature dependence of opti- cal properties of gas source MBE	82/83 (1994) 46	Temperature-programmed-desorption study of the process of atomic deu- terium adsorption onto Si(100)2 × 1, M. Suemitsu, H. Nakazawa and N.	,
grown GaP/AIP short period super- lattices, J.H. Kim, H. Asahi, K. Asami, K. Iwata, S.G. Kim and S. Gonda Fabrication of CuO ₂ -plane-based high-	82/83 (1994) 76	Miyamoto Observation of the interface of Ba/Si(100) by MDS and TDS, S.	82/83 (1994) 449
temperature superconducting thin films by atomic layer controlled molecular beam epitaxy, I. Yoshida,		Hongo, K. Ojima, S. Taniguchi, T. Urano and T. Kanaji	82/83 (1994) 537
H. Furukawa, T. Hirosawa and M. Nakao	82/83 (1994) 501	Thin films Recent advances in atomic layer epitaxy	
Surface composition		devices, S.M. Bedair and N.A. El- Masry Atomic layer epitaxy growth of doped	82/83 (1994) 7
Surface stoichiometry and the role of ad- sorbates during GaAs atomic layer epitaxy, J.R. Creighton	82/83 (1994) 171	zinc oxide thin films from organomet- als, V. Lujala, J. Skarp, M. Tammen- maa and T. Suntola	82/83 (1994) 34
cpitaly, J.R. Cleighton	02/03 (1777) 1/1	anno dila 1. Daniola	4-, 00 (1221) 54

Atomic layer epitaxy in the growth of complex thin film structures for elec-		X-ray diffraction	
troluminescent applications, L. Niin- istö and M. Leskelä In situ ellipsometric diagnostics for con- trolled growth of metal oxides with	82/83 (1994) 454	Growth temperature dependence of opti- cal properties of gas source MBE grown GaP/AlP short period super- lattices, J.H. Kim, H. Asahi, K. Asami,	
surface chemical reactions, H. Kuma- gai and K. Toyoda Layer controlled growth of oxide super- conductors, M. Kawai, ZY. Liu, T. Hanada, M. Katayama, M. Aono and	82/83 (1994) 481	K. Iwata, S.G. Kim and S. Gonda Selective epitaxial growth of GalnP by LP-MOCVD using ethyldimeth- ylindium, trimethylindium, trimethyl- gallium and triethylgallium as group	82/83 (1994) 76
C.F. McConville Preparation of ultra-flat YBCO thin films by MOCVD layer-by-layer deposition,	82,/83 (1994) 487	III sources, SH. Chan, S.M. Sze, CY. Chang and WI. Lee Microscopic analysis of interface struc-	82/83 (1994) 85
M. Matsubara and I. Hirabayashi Oxidation of TiN thin films in an ion- beam-assisted deposition process, H. Kubota, M. Nagata, R. Miyagawa and	82/83 (1994) 494	ture in InGaAs/InP MQW using Pendellösung oscillation around a satellite peak in high-resolution X-ray	
M.A. Nicolet	82/83 (1994) 565	diffraction, M. Takemi, T. Kimura, K. Mori, K. Goto, Y. Mihashi and S. Takamiya	82/83 (1994) 115
Time of flight techniques		Growth of In ₂ S ₃ thin films by atomic layer epitaxy, T. Asikainen, M. Ritala and M. Leskelä	92 /92 (1004) 122
Pulsed trimethylgallium scattering from As-stabilized and Ga-stabilized sur-		Role of a metalorganic As source in atomic layer epitaxy of GaAs and	82/83 (1994) 122
faces, M. Sasaki and S. Yoshida	82/83 (1994) 269	AlAs, I. Suemune Preparation of ultra-flat YBCO thin films by MOCVD layer-by-layer deposition,	82/83 (1994) 149
Titanium		M. Matsubara and I. Hirabayashi Fabrication of CuO ₂ -plane-based high-	82/83 (1994) 494
Structural study of SrTiO ₃ (100) surfaces by low energy ion scattering, Y. Tanaka, H. Morishita, M. Watamori, K. Oura and I. Katayama	82/83 (1994) 528	temperature superconducting thin films by atomic layer controlled molecular beam epitaxy, I. Yoshida, H. Furukawa, T. Hirosawa and M. Nakao	82/83 (1994) 501
Titanium nitride		The effect of growth parameters on the deposition of CaS thin films by atomic layer epitaxy, J. Rautanen, M.	
Oxidation of TiN thin films in an ion- beam-assisted deposition process, H.		Leskelä, L. Niinistö, E. Nykänen, P. Soininen and M. Utriainen	82/83 (1994) 553
Kubota, M. Nagata, R. Miyagawa and M.A. Nicolet	82/83 (1994) 565	X-ray fluorescence	
Tungsten		The effect of growth parameters on the deposition of CaS thin films by atomic layer epitaxy, J. Rautanen, M. Leskelä, L. Niinistö, E. Nykänen, P.	
Surface structure dependence of ${\rm O_2-W}$ adsorption system, M. Sato	82/83 (1994) 532	Soininen and M. Utriainen	82/83 (1994) 553
		X-ray spectroscopy	
Water		NbCl ₅ as a precursor in atomic layer epitaxy, KE. Elers, M. Ritala, M.	
Adsorption and desorption of H ₂ O on potassium precovered Si(100)2 × 1 surface, S. Hongo, S. Taniguchi, K.		Leskelä and E. Rauhala Preparation of ultra-flat YBCO thin films by MOCVD layer-by-layer deposition,	82/83 (1994) 468
Ojima, T. Urano and T. Kanaji	82/83 (1994) 437	M. Matsubara and I. Hirabayashi	82/83 (1994) 494

Zeolites

Theoretical estimation of ordered metal

probing method, A. Yoshikawa, M. Kobayashi and S. Tokita

82/83 (1994) 316

Zinc oxide

- species in zeolite pores, H. Himei, E. Maruya, M. Kubo, R. Vetrivel and A. Miyamoto
- Atomic layer epitaxy growth of doped 82/83 (1994) 543 zinc oxide thin films from organometals, V. Lujala, J. Skarp, M. Tammenmaa and T. Suntola
- 82/83 (1994) 34

- Zinc
- Atomic layer epitaxy of ZnSe using reflectance difference spectroscopy, H.
- Akinaga and K. Tanaka Surface reaction mechanism in MOMBE-ALE of ZnSe and CdSe as determined by a new in-situ optical
- CO adsorption on clean and atomiclayer-Cu-covered ZnO(1010) surfaces, Q. Ge and P.J. Møller 82/83 (1994) 298
 - Influence of atomic Cu-layer epitaxy on CO2 and CO photoinduced desorption from ZnO(0001), P.J. Møller, S.A. Komolov and E.F. Lazneva
- 82/83 (1994) 305
 - 82/83 (1994) 569



